

The lonely perpetrator in the DCDC FEAST2 case

How an individual transistor threatened the operation of the CMS pixel detector

F.Faccio, CERN, EP-ESE

S.Michelis, G.Ripamonti, D.Porret
CERN, EP-ESE

F. Szoncsó
CERN, HSE-DI

D. Valuch
CERN, BE-RF-FB

N. Bacchetta, S. Cuadrado Calzada, A. Karneyeu, T. Prousalidi, M. Hansen, A. Kaminski, S. Lusin + many others
CMS team

These slides have been prepared solely for the purpose of supporting an oral presentation and are not suitable to convey a clear message outside this context.

A full report as well as an executive report are available at the following link:

<http://project-dcdc.web.cern.ch/project-DCDC/public/Reports.html>

Investigation = the act or process of examining a crime, problem, statement, etc. carefully, especially to discover the truth



The truth about the FEAST2 affair

The crime scene

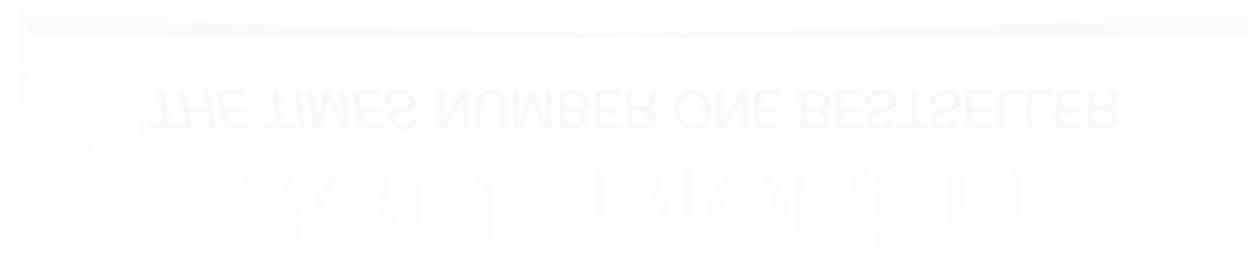
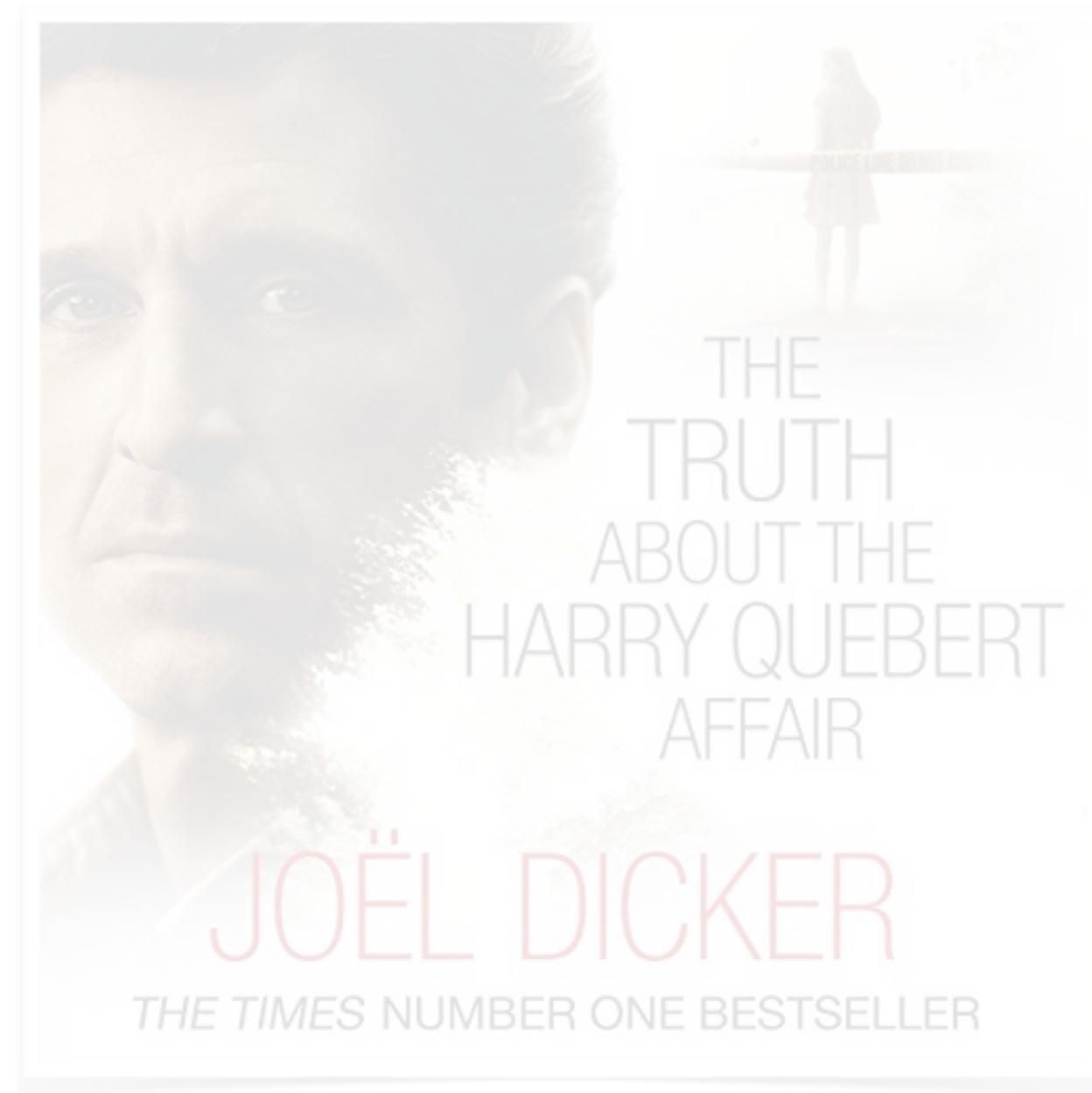
Witnesses

The autopsy

The motive

The crime reconstruction

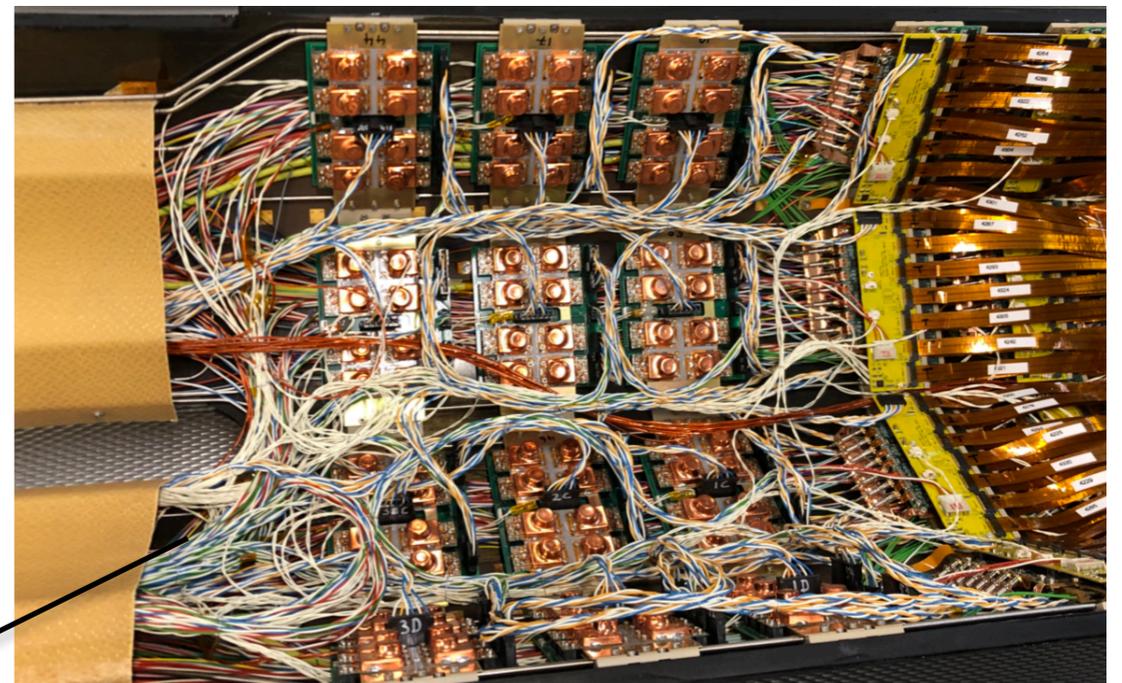
The perpetrator



The crime scene

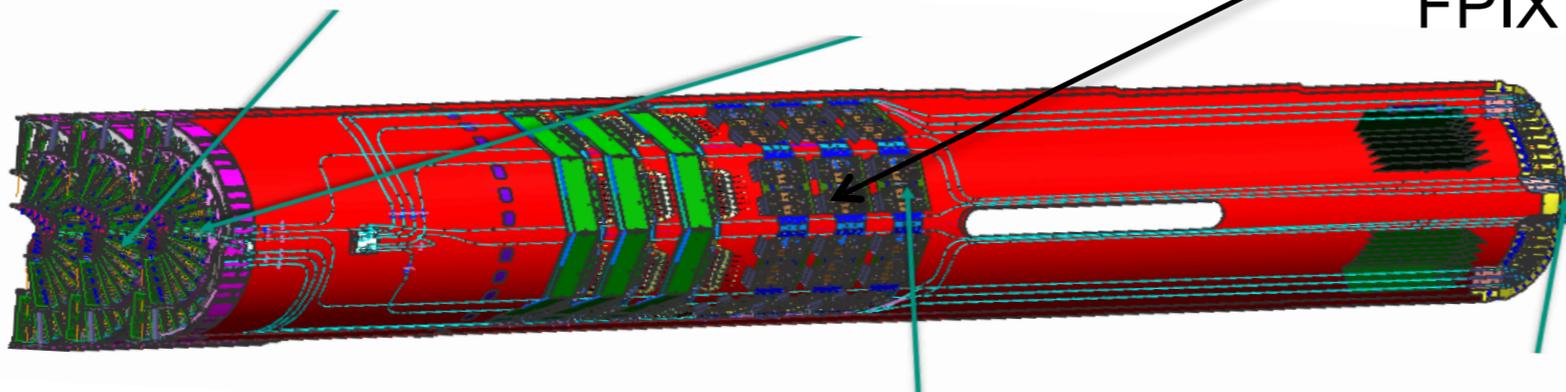


FEAST2 in the CMS pixel detector



FPIX

384 in total

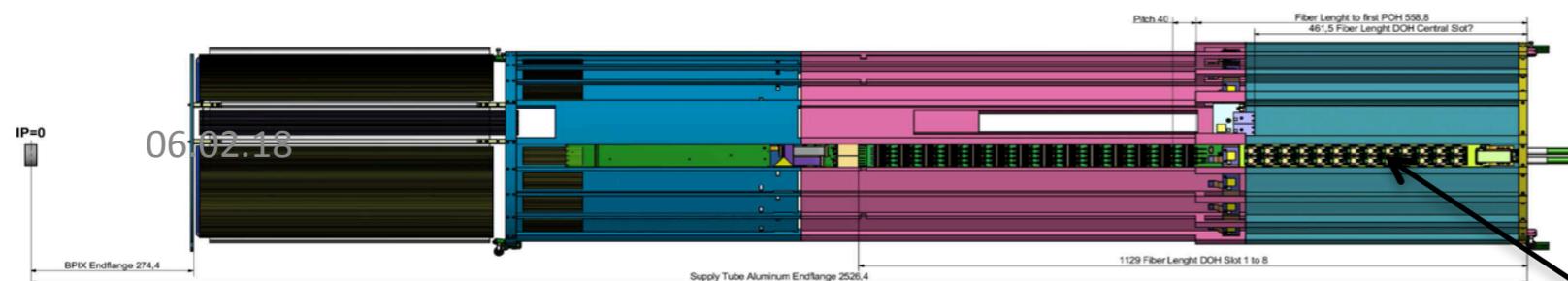


IP

Bpix DC-DC: radius 240mm, z range 2067- 2430mm from i/p.
 Fpix DC-DC: radius 140mm, z range 1315-1530mm from i/p

BPIX

832 in total

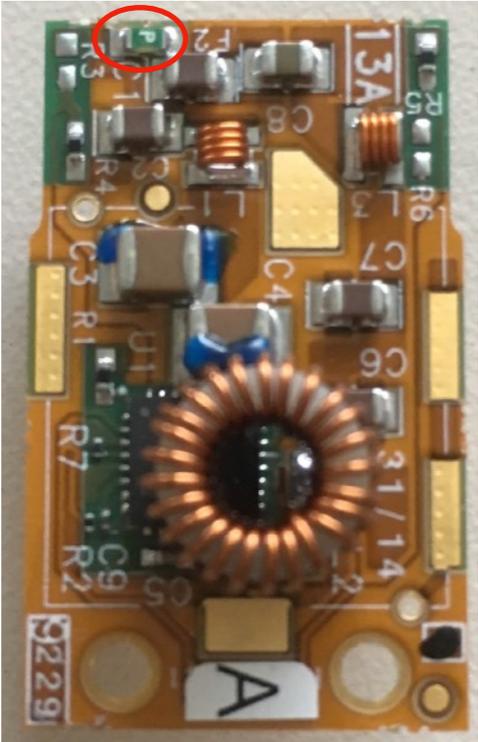


Cooling at -20°C

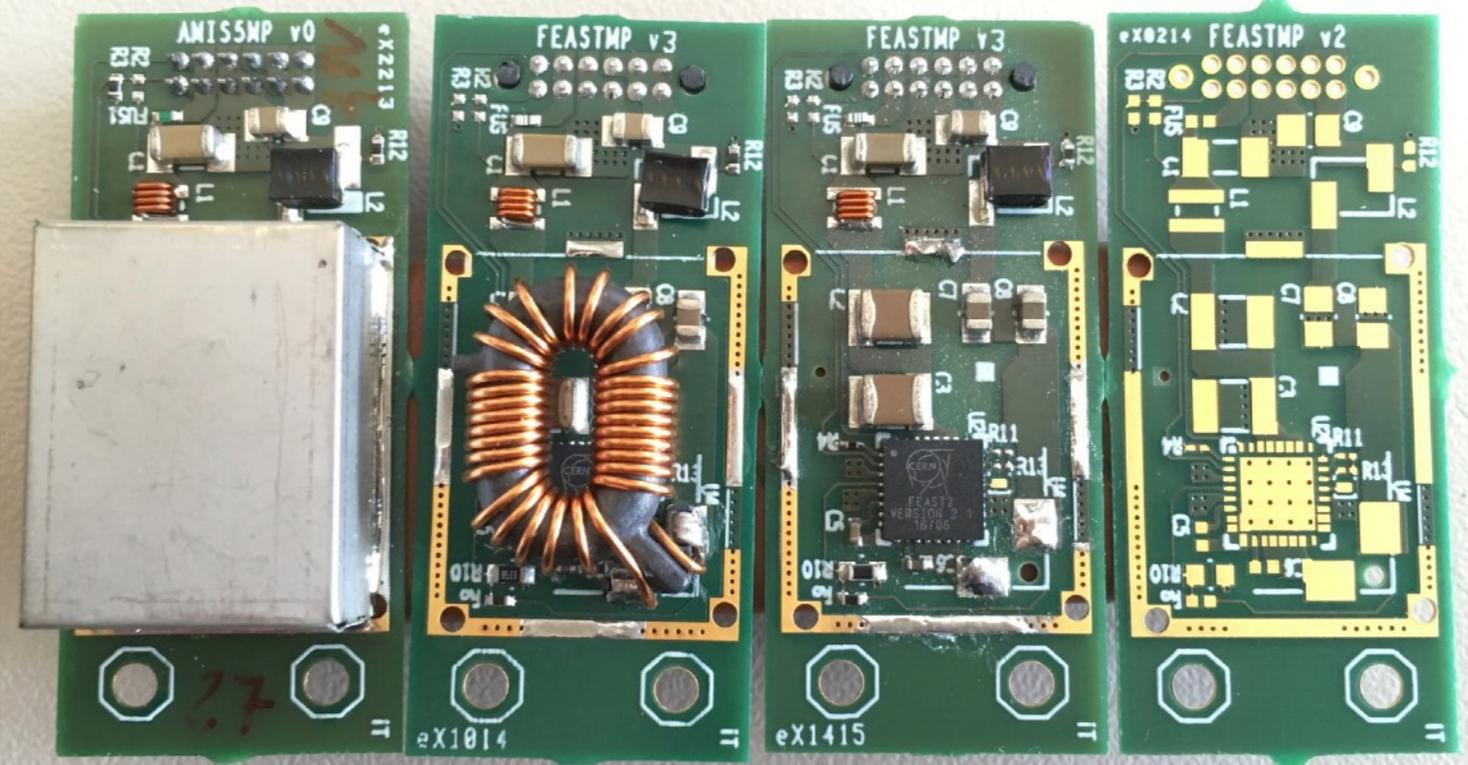
Module in the CMS pixels

Module everywhere else

This fuse prevents the lowering of Vin



Aachen module



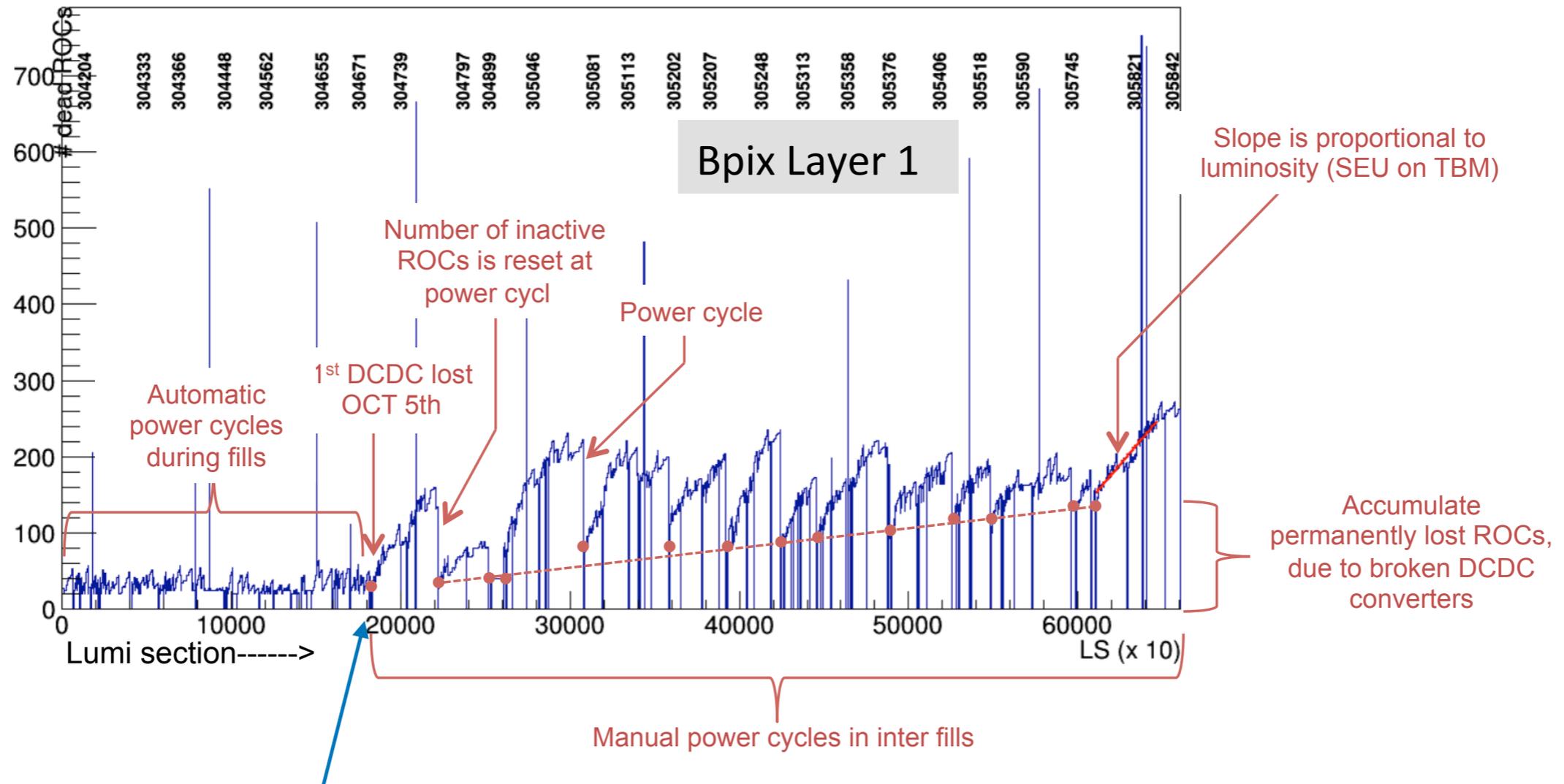
CERN module (FEASTMP)



Witnesses



Failure of FEAST DCDCs in the CMS pixel detector



Increase in luminosity, change in beam structure

No correlation with:

- output voltage
- output current
- position in the detector
- anything other than the beam

DCDCs fail during disable/enable cycles

Plan around November 2017

Rest of 2017 Physics Run

Nothing can be done.
Accept loss of modules



YETS 17-18

Request longer Year-End Stop
Open the detector
Extract all DCDC modules
Replace (all?) modules (fuse changed)



2018 Physics Run

Find a patch ensuring
data taking



LS2

Solve the problem
for the long term

⋮
“At this pace, game over
for CMS around May 2018”
⋮

The autopsy



YETS 17-18: Merry Christmas!

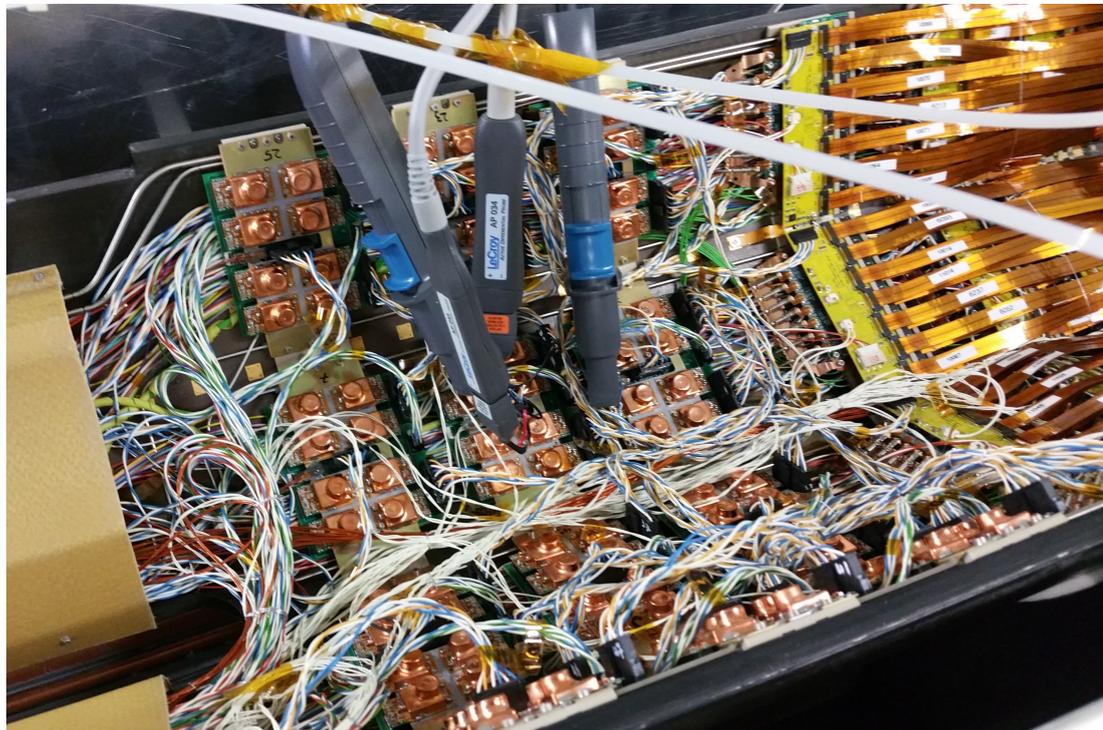
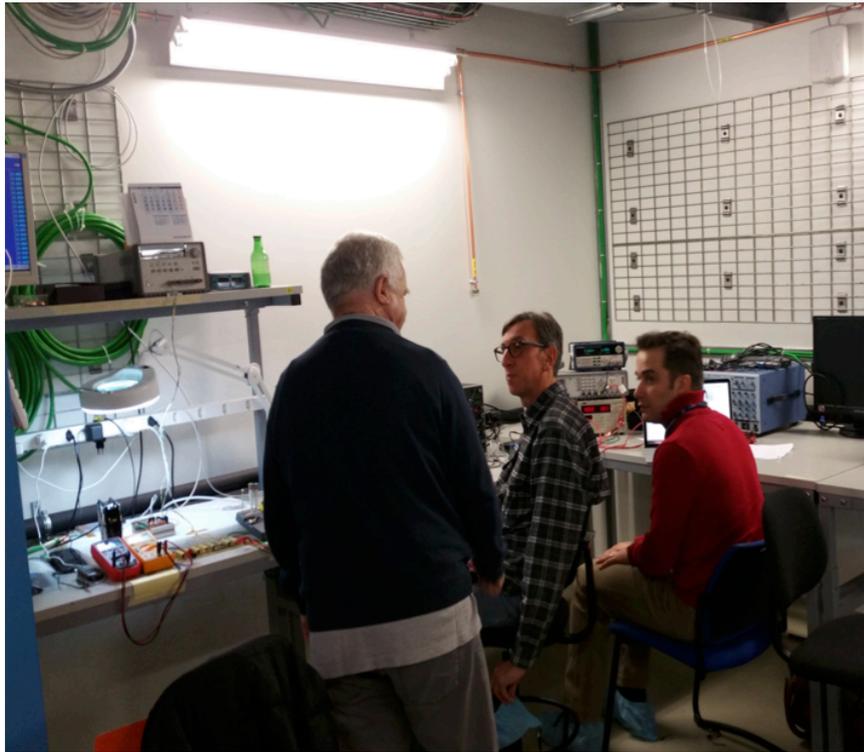


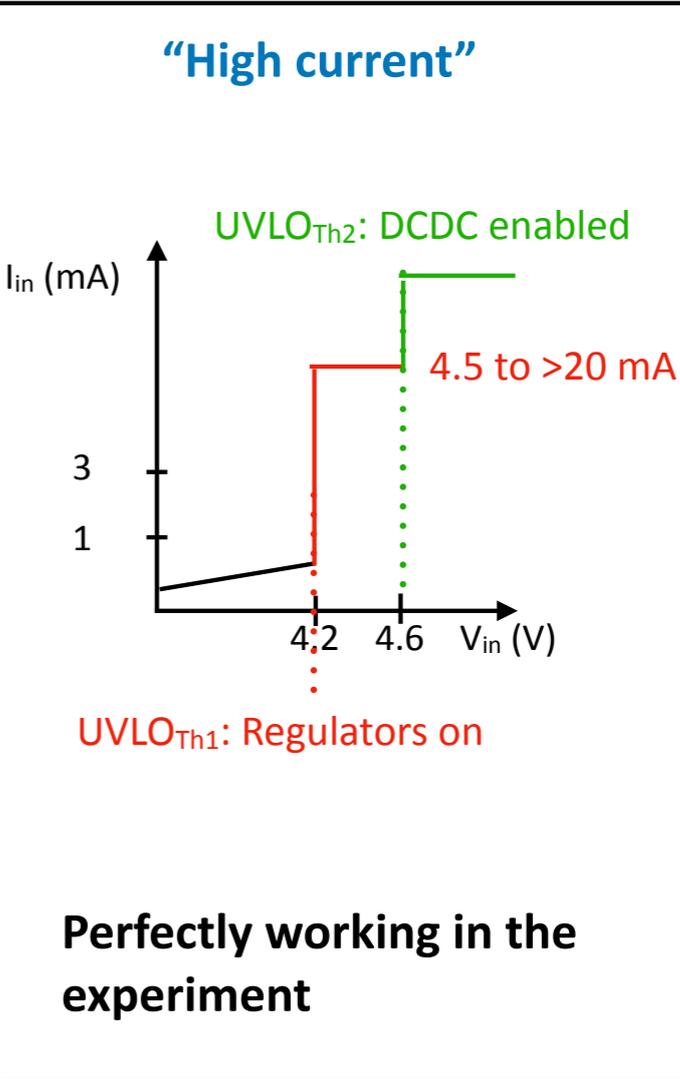
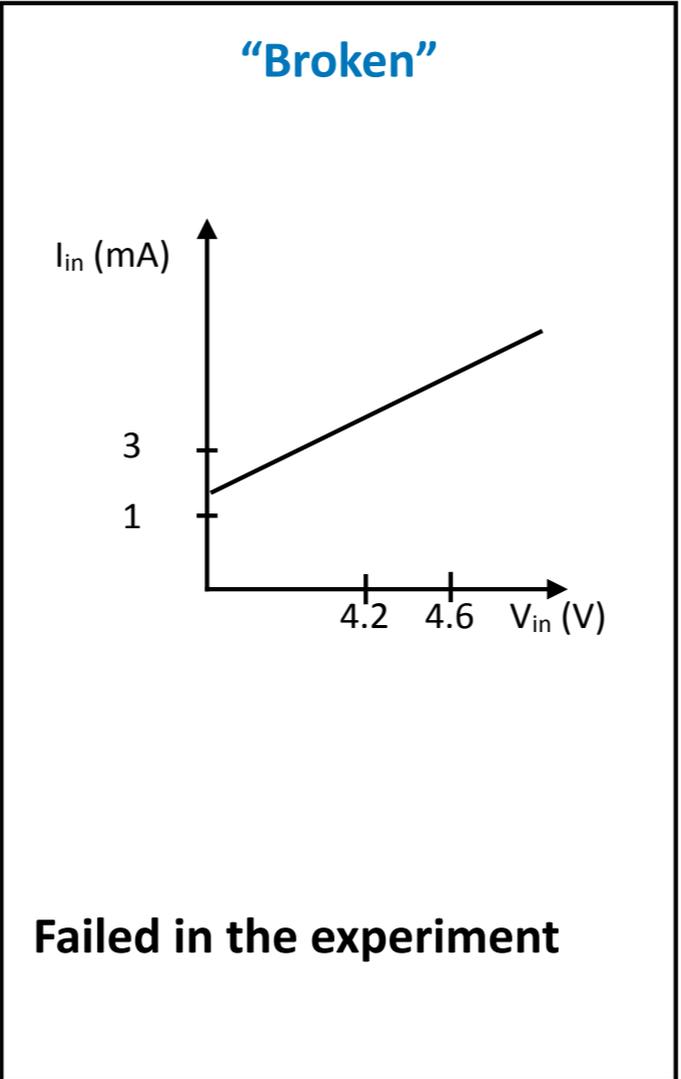
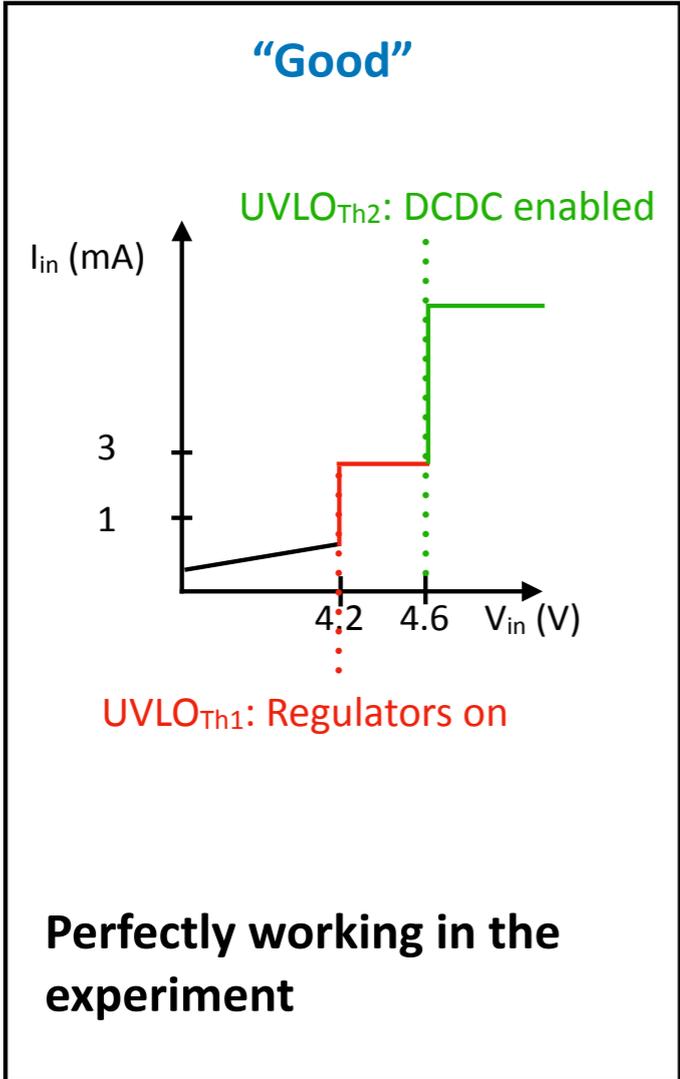
Photo memories from the 2017 Christmas Break

FEAST2 modules in the CMS experiment were found to present 2 distinct types of damage

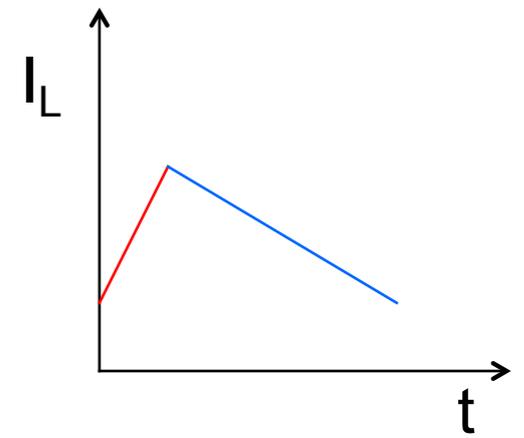
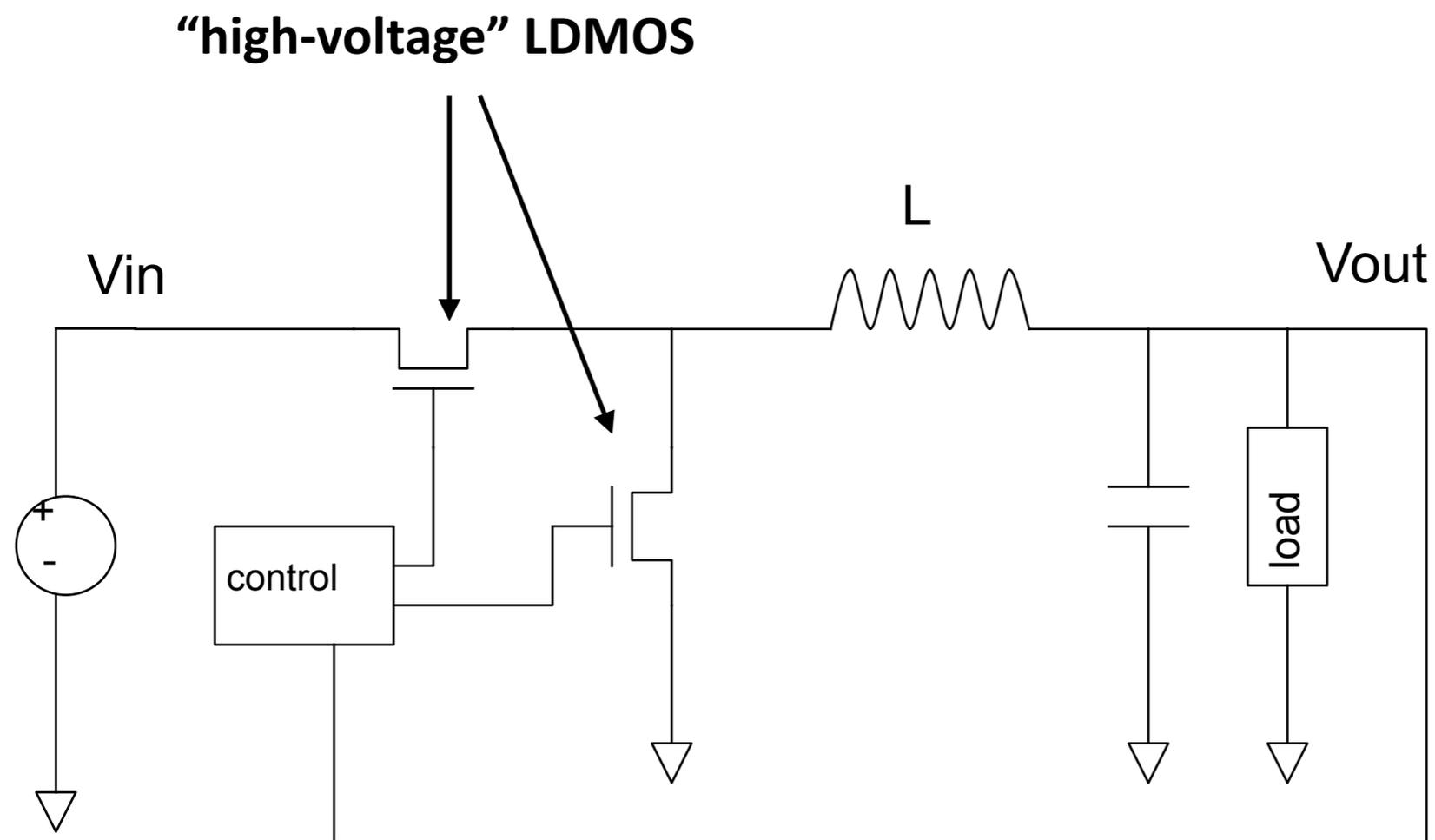
- “Broken” samples failed to provide any output voltage
- “High-current” samples were perfectly functional, but were found to have an excessive current below UVLO

Perfectly working in the system but found to have anomalous current when tested

Pixel Names	Number of Converters	Tested Broken	Tested working with High Current	Tested working with normal current	BROKEN	HIGH CURRENT	
		"BROKEN"	"HIGH CURRENT"	"GOOD"	% with respect to total	% with respect to total working	
BPIX (+Z, Near)	BPIX-Bpl	208	4	48	156	1.9	23.5
BPIX (-Z, Near)	BPIX-Bml	208	10	48	150	4.8	24.2
BPIX (+Z, Far)	BPIX-BpO	208	13	70	125	6.3	35.9
BPIX (-Z, Far)	BPIX-BmO	208	11	70	127	5.3	35.5
FPIX (+Z, Near)	FPIX-Bpl	96	7	41	48	7.3	46.1
FPIX (-Z, Near)	FPIX-Bml	96	7	34	55	7.3	38.2
FPIX (+Z, Far)	FPIX-BpO	96	9	23	64	9.4	26.4
FPIX (-Z, Far)	FPIX-BmO	96	6	22	68	6.3	24.4
BPIX - not connected to modules		32	2	8	22	6.3	26.7

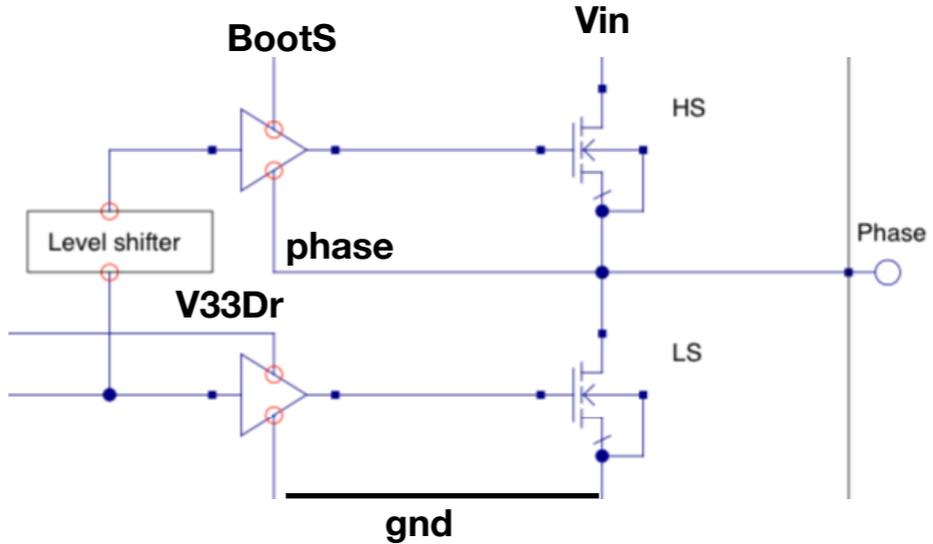
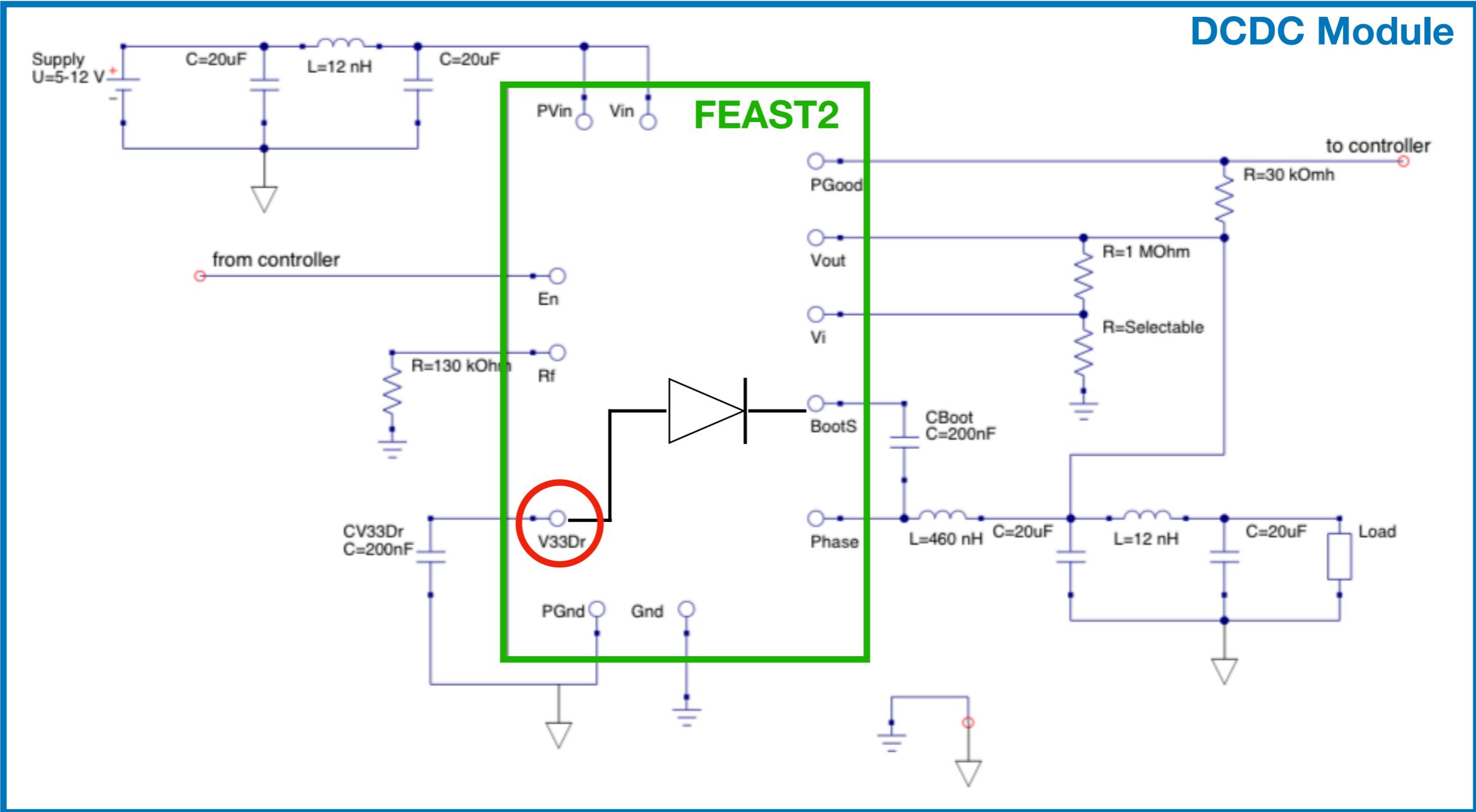


Operation of a switching converter

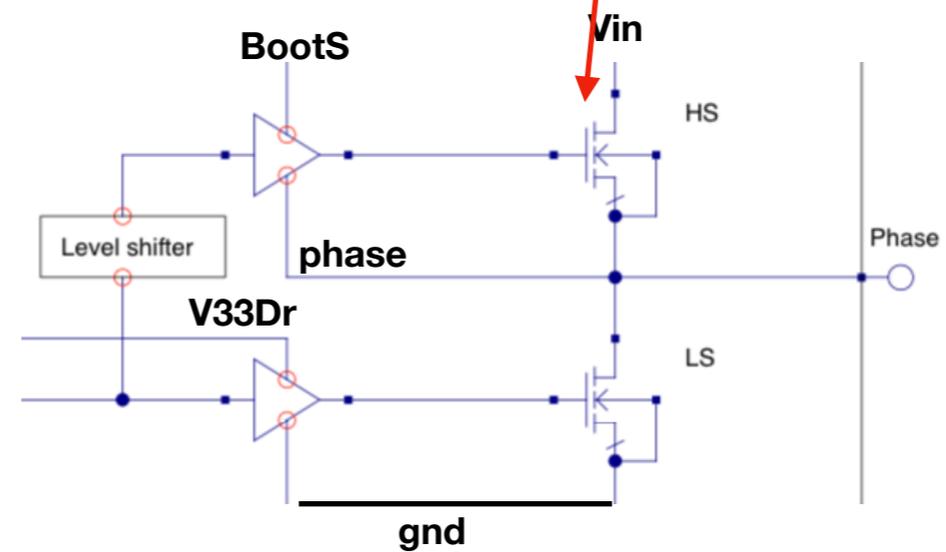
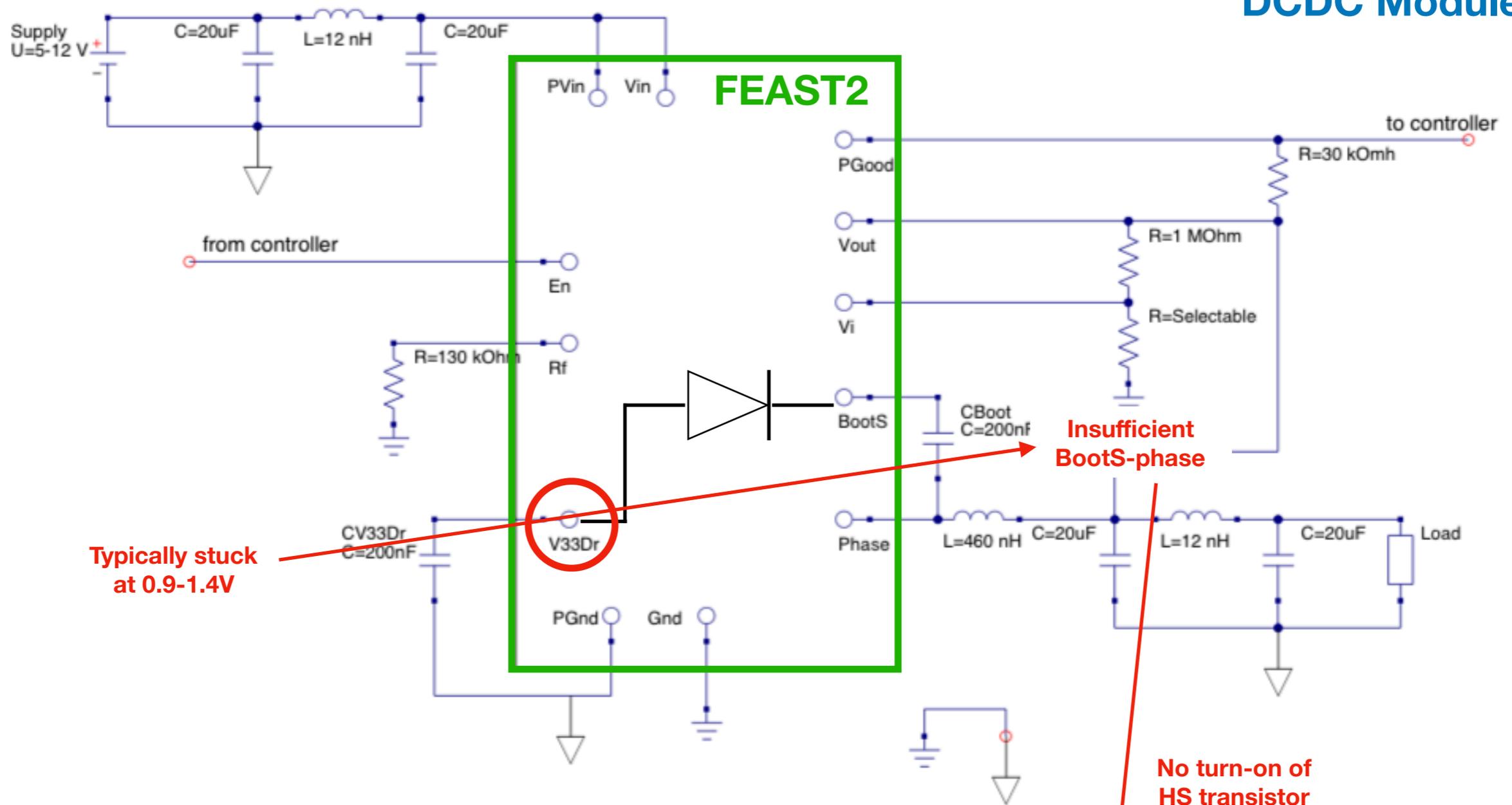


$$\frac{V_{out}}{V_{in}} = \text{Duty cycle}$$

DCDC Module

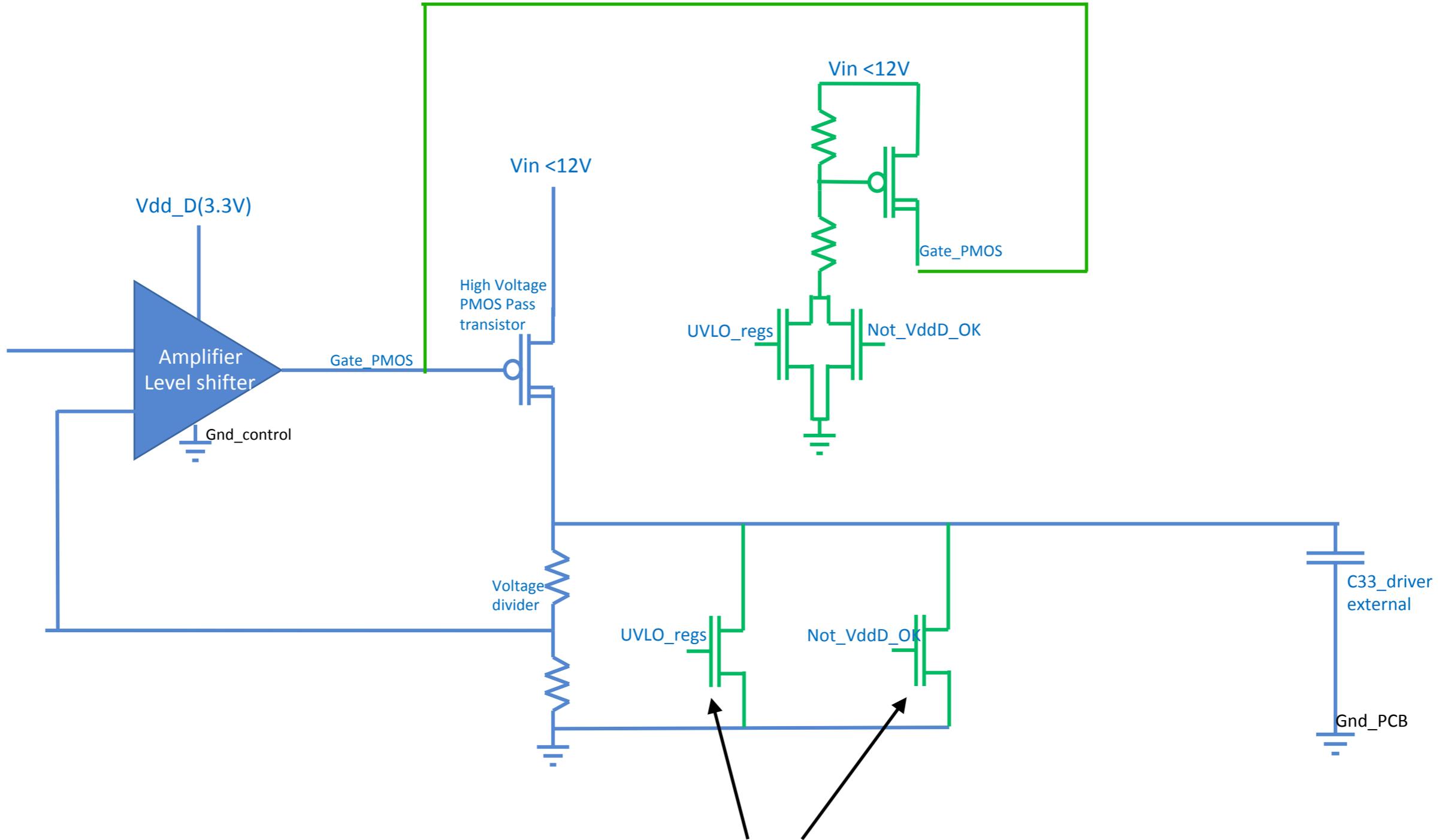


DCDC Module



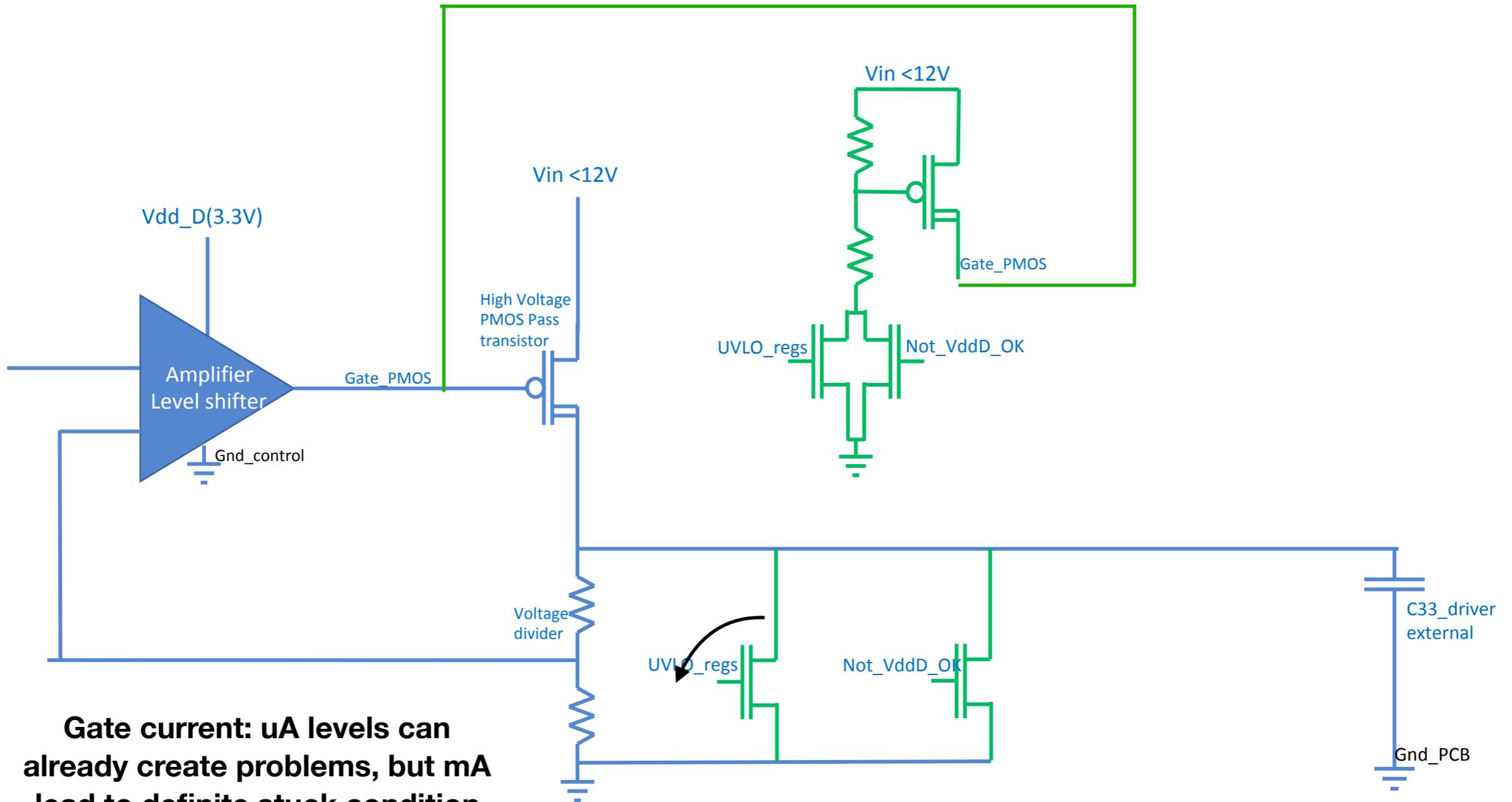
On-chip V33Dr regulator with clamps

Green elements are only used under UVLO Thresholds



**Clamp transistors for soft-start procedure
(transistors rated to 3.3V)**

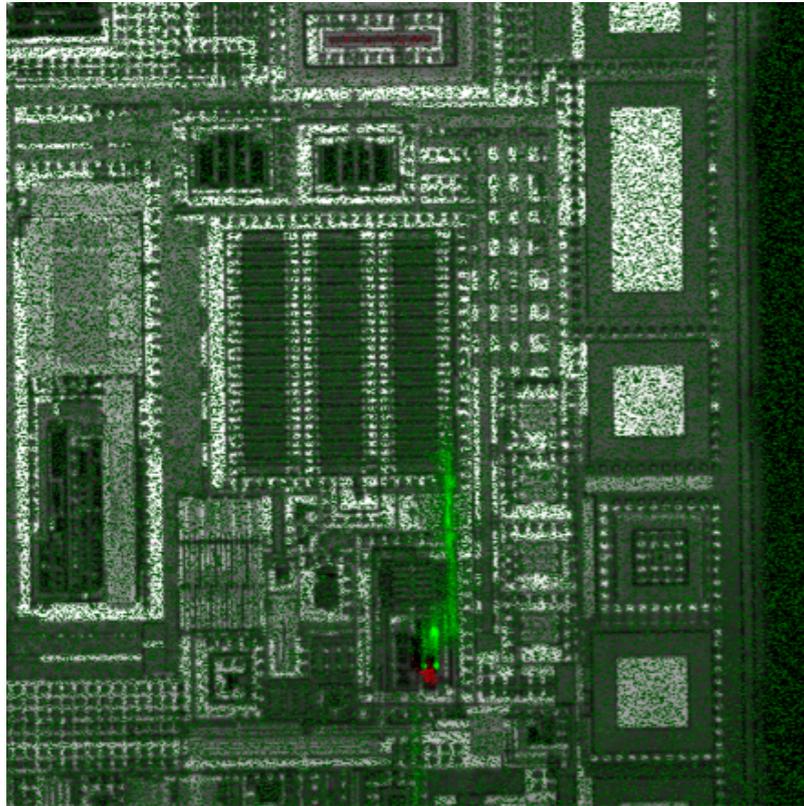
What happens if the clamp transistors are damaged?



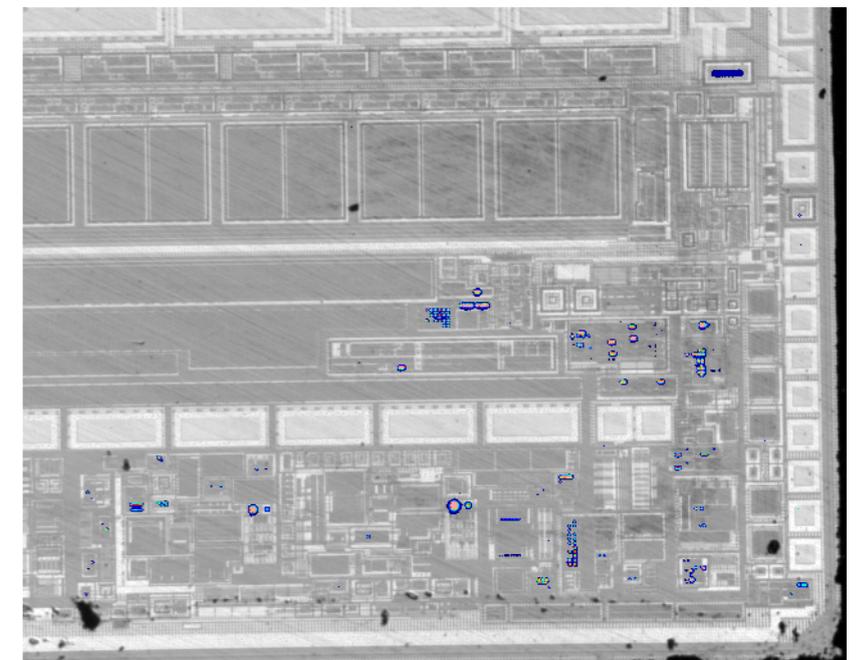
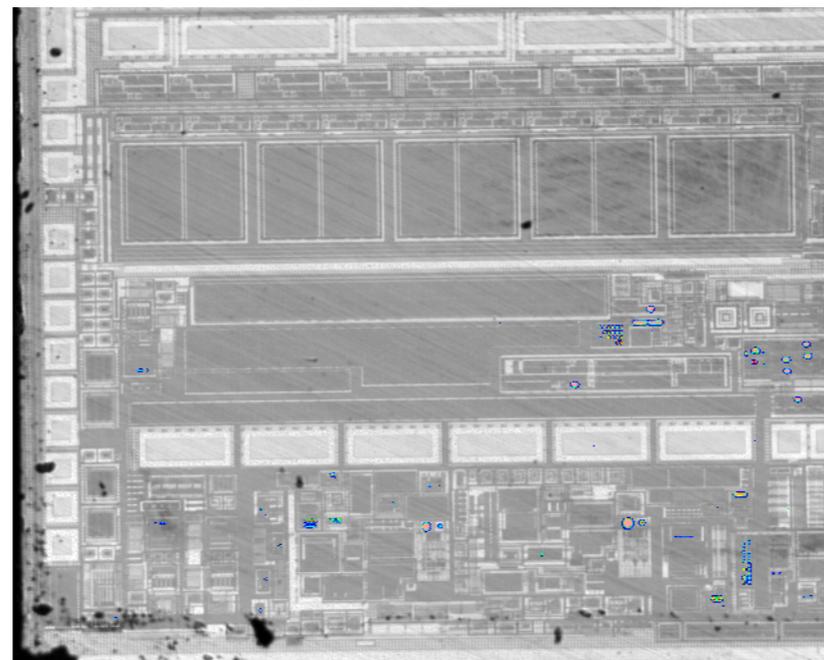
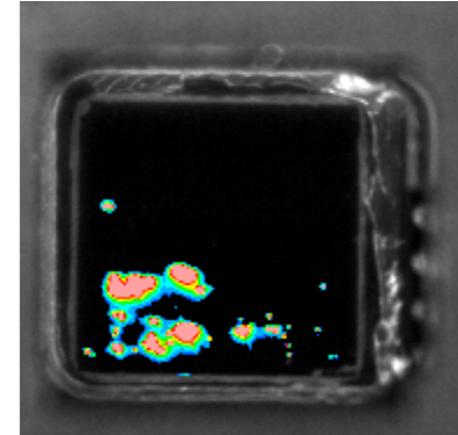
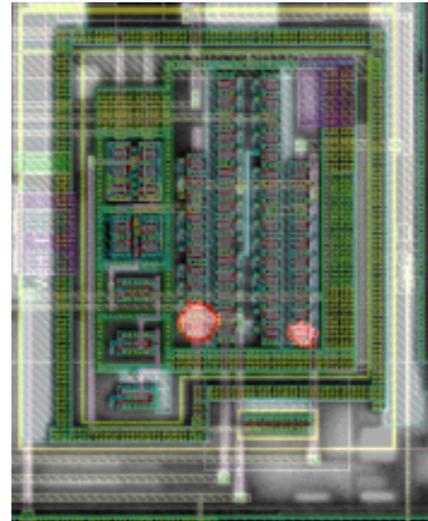
Gate current: μA levels can already create problems, but mA lead to definite stuck condition

This also disrupts the correct value of the $UVLO_regs$ voltage, hence preventing the UVLO from working correctly

Failure Analysis (FA) with emission microscopy and Optical Beam Induced Resistance Change (OBIRCH) at MASER (NL)



During OBIRCH a laser beam selectively illuminates the metal lines, altering their resistance. The consequent input current change is measured, allowing the mapping of current paths. In broken FEAST2 samples, current flows to the clamp transistors.



Emission images are based on the detection of photons generated from hot carriers (therefore only conducting NMOS transistors are well visible). "Broken" or "High-current" FEAST2 samples showed different current paths.

The motive



Why the clamp transistor(s) is(are) damaged?

Flawed ASICs?

Flawed PCBs?

Radiation in ASIC?

EM noise?

Radiation in package?

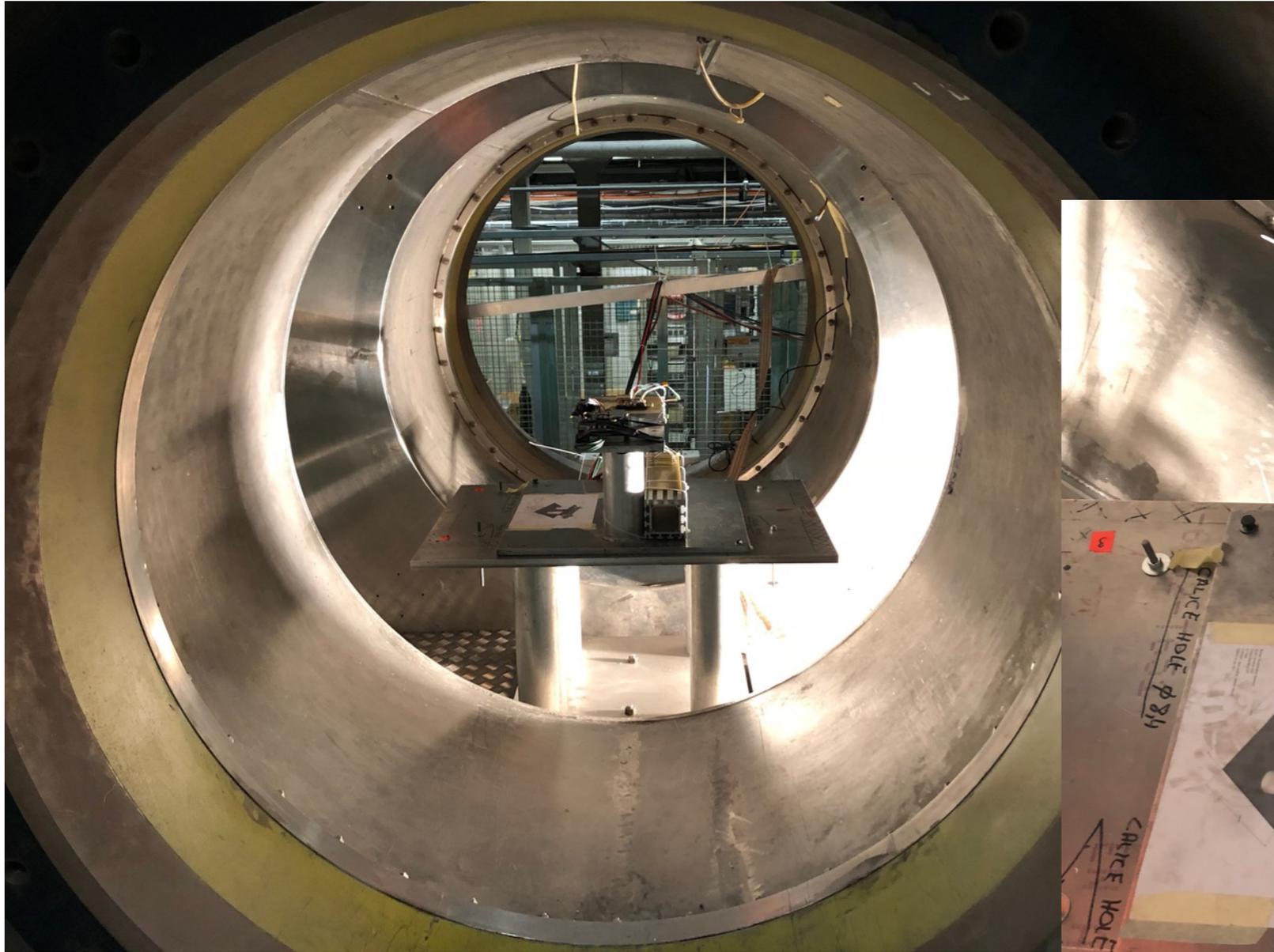
Environmental conditions?

Electrical stress?

Combination of any of the above??

Environmental conditions?

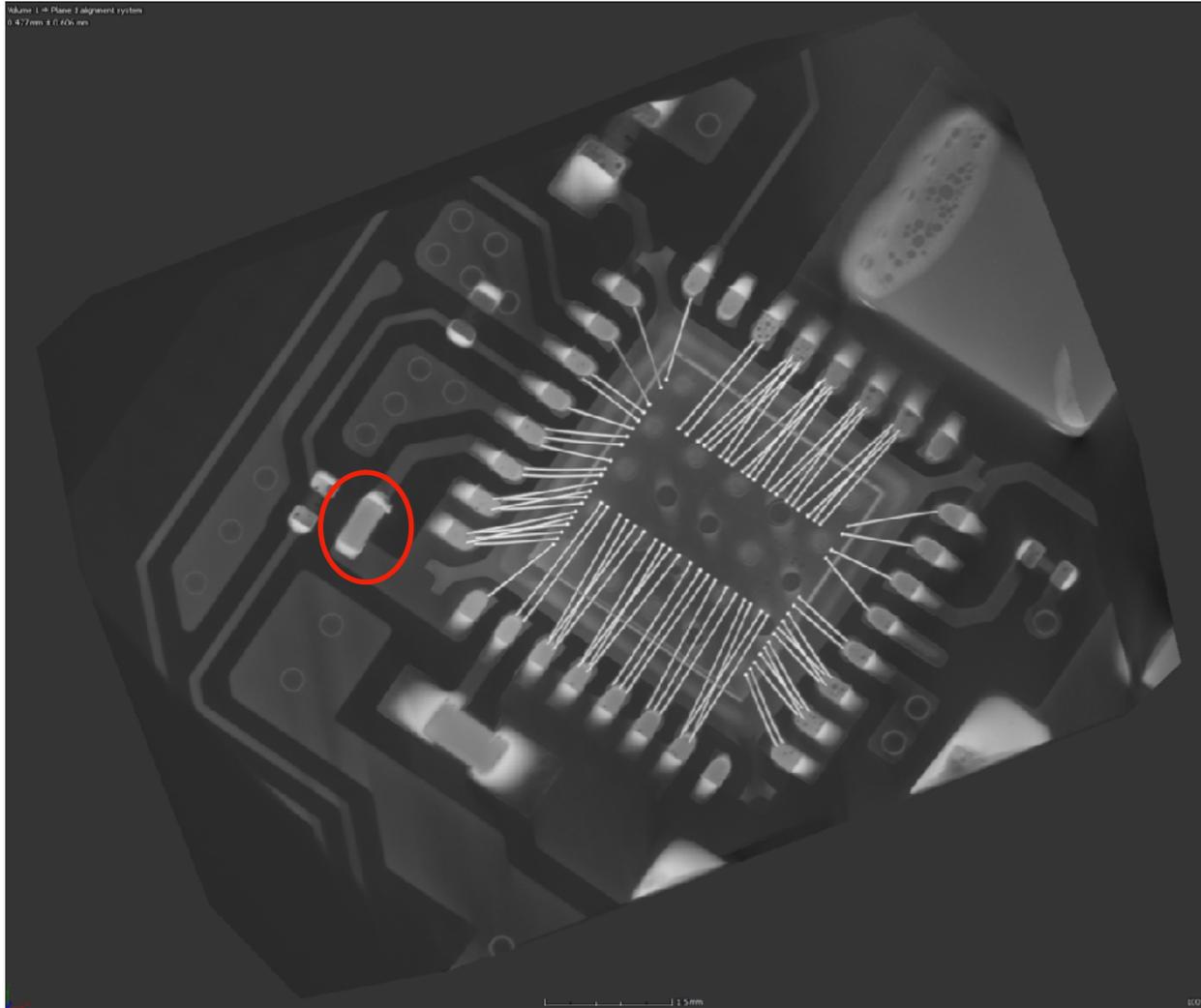
Test in a 3T magnetic field revealed no problem



FEASTMP and CMS modules inside the M1 facility in the H2 beam line in Prévessin (Building 887)

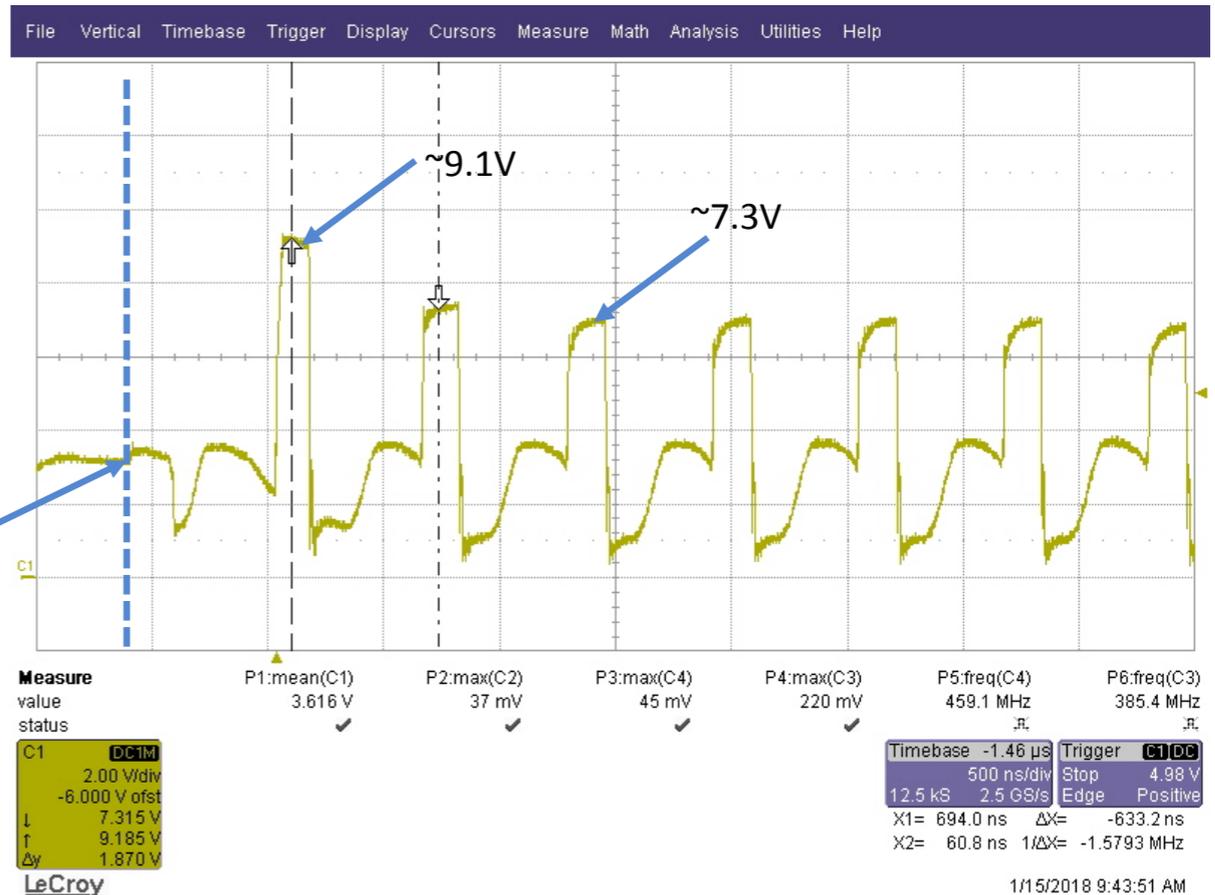
Flawed PCBs?

Faulty capacitor, or intermittent contacts of the capacitor in the PCB generated a stress that produced somewhat similar damage



3D X-ray imaging of the module to inspect the quality of the soldering of the capacitor to the PCB

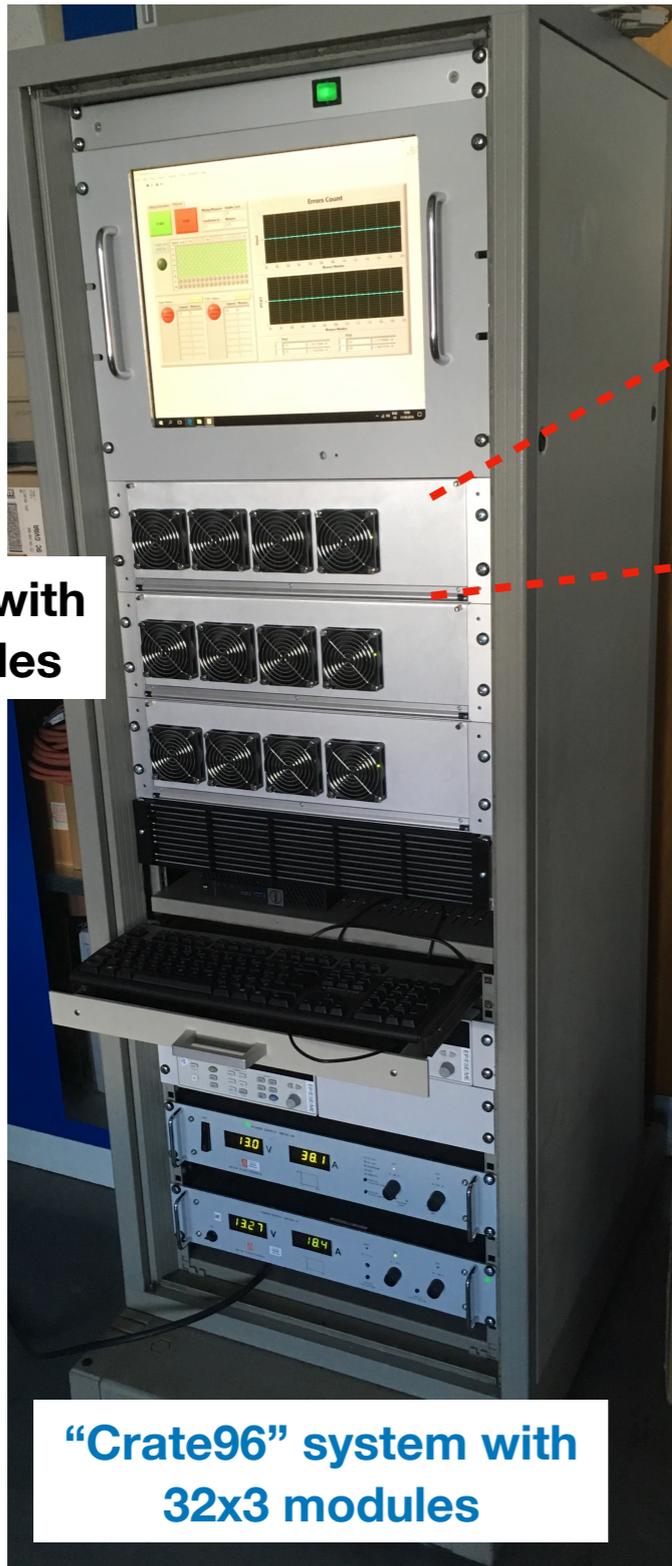
Cap removed



Waveform of the V33Dr node when the capacitance has intermittent contacts to the PCB

Electrical stress?

Long-term ageing tests on 124 converters did not reveal problems with FEAST2 ASICs

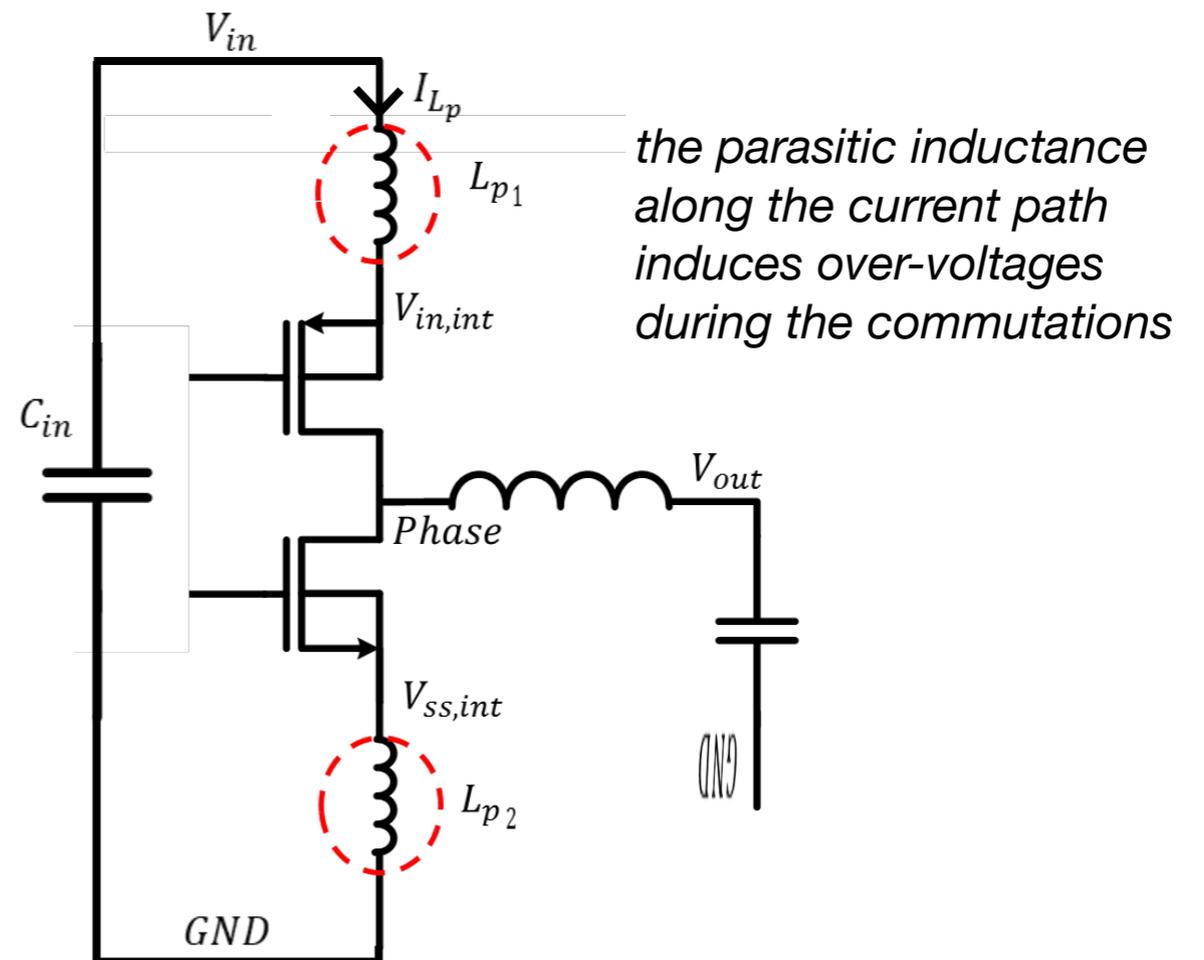


3 drawers with
8x4 modules

“Crate96” system with
32x3 modules



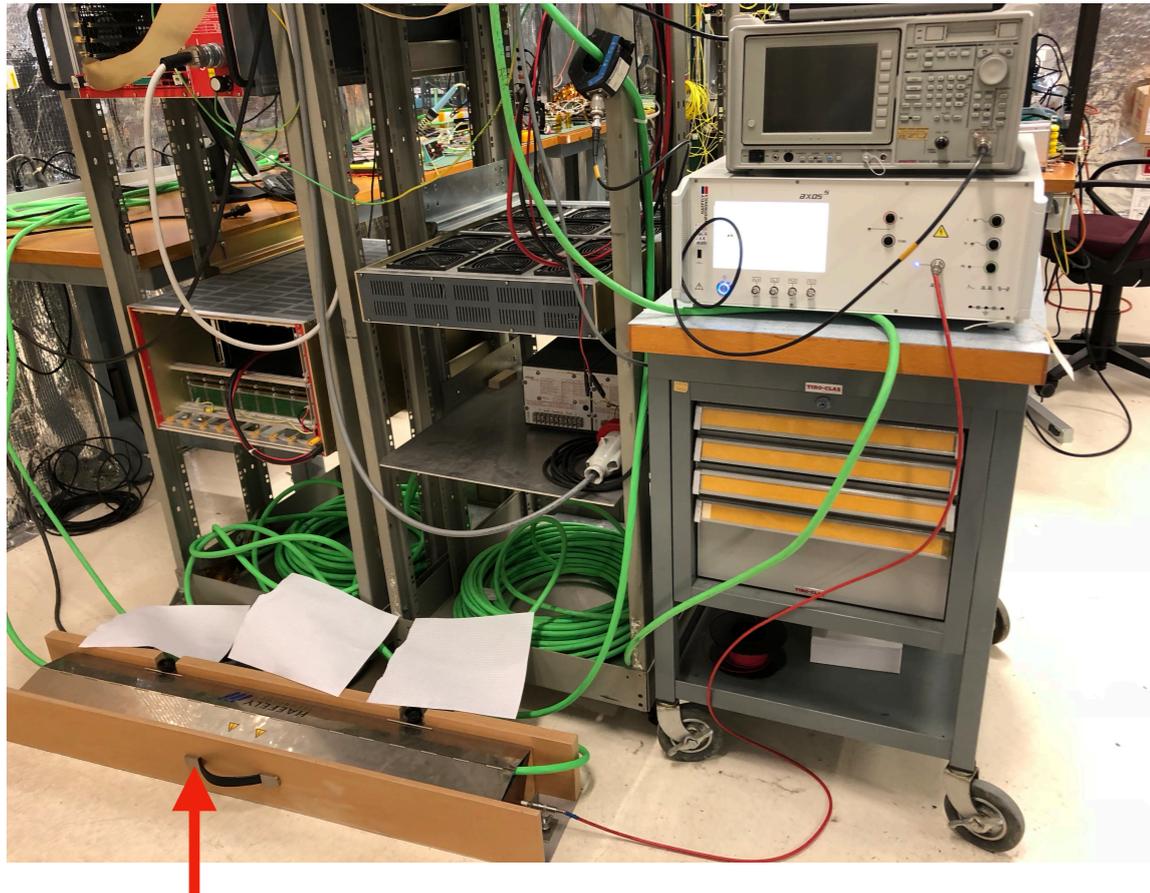
view of an
open drawer



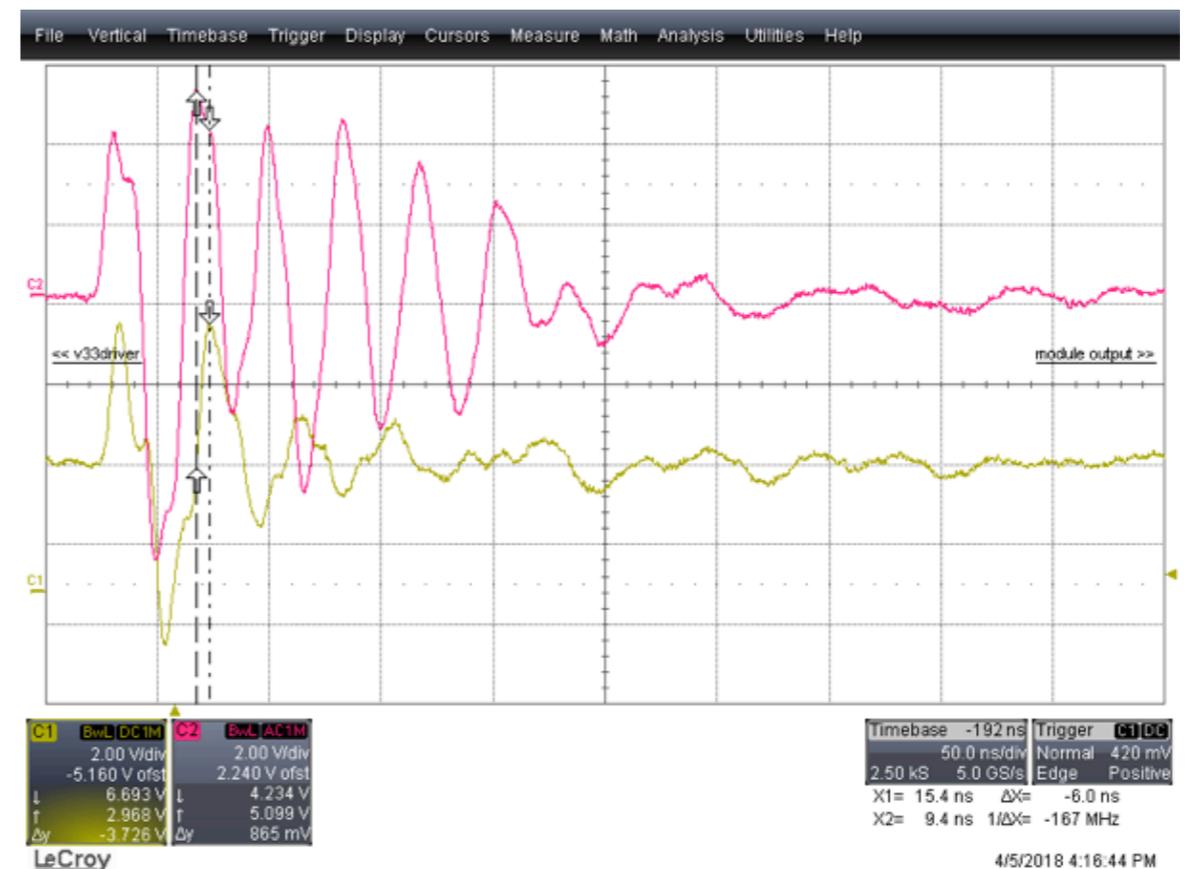
EM noise? Environmental conditions?

Injection of EM noise by capacitive coupling to the input/output and signal lines. The converter appears to be very resilient

Led by F. Szoncsó and D. Valuch



Capacitive high-frequency coupler used on the input bus line



AC-observation of the effect of a 3kV (!) pulse with 50ns duration on V_{in} and V_{33Dr} . The peak is several V above the DC (V_{33Dr} reaches 8V)!

EM noise? Environmental conditions?

High-frequency, large power RF noise injection could produce damage with different signature

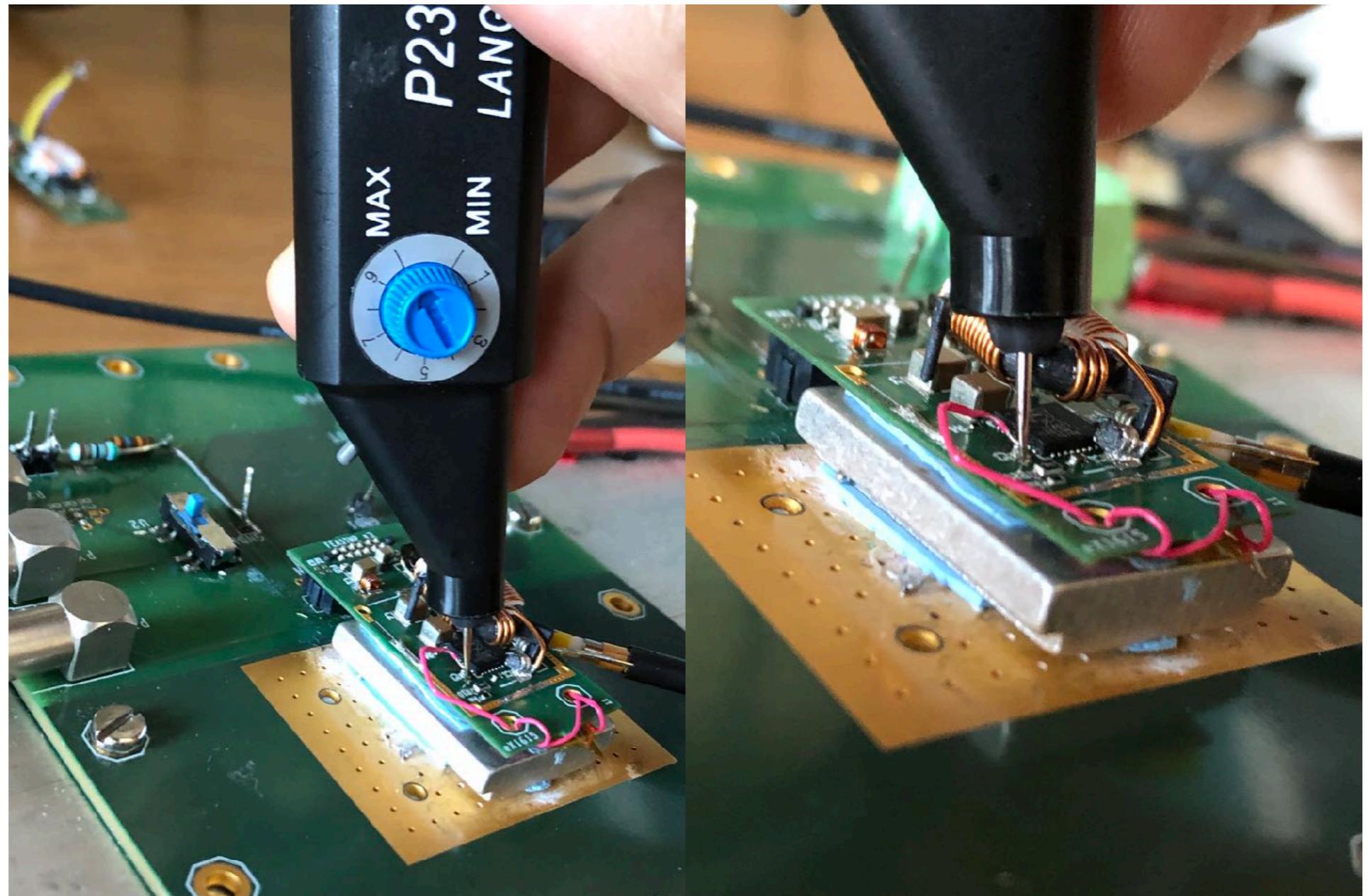
Led by F. Szoncsó and D. Valuch



High frequency (GHz) and high power transient pulses are injected via an antenna in a special chamber in CERN Prévessin. At very large power, the ASIC can be damaged but the signature is different than in samples failing in CMS. Coupling is through the long enable line.

EM noise? Environmental conditions?

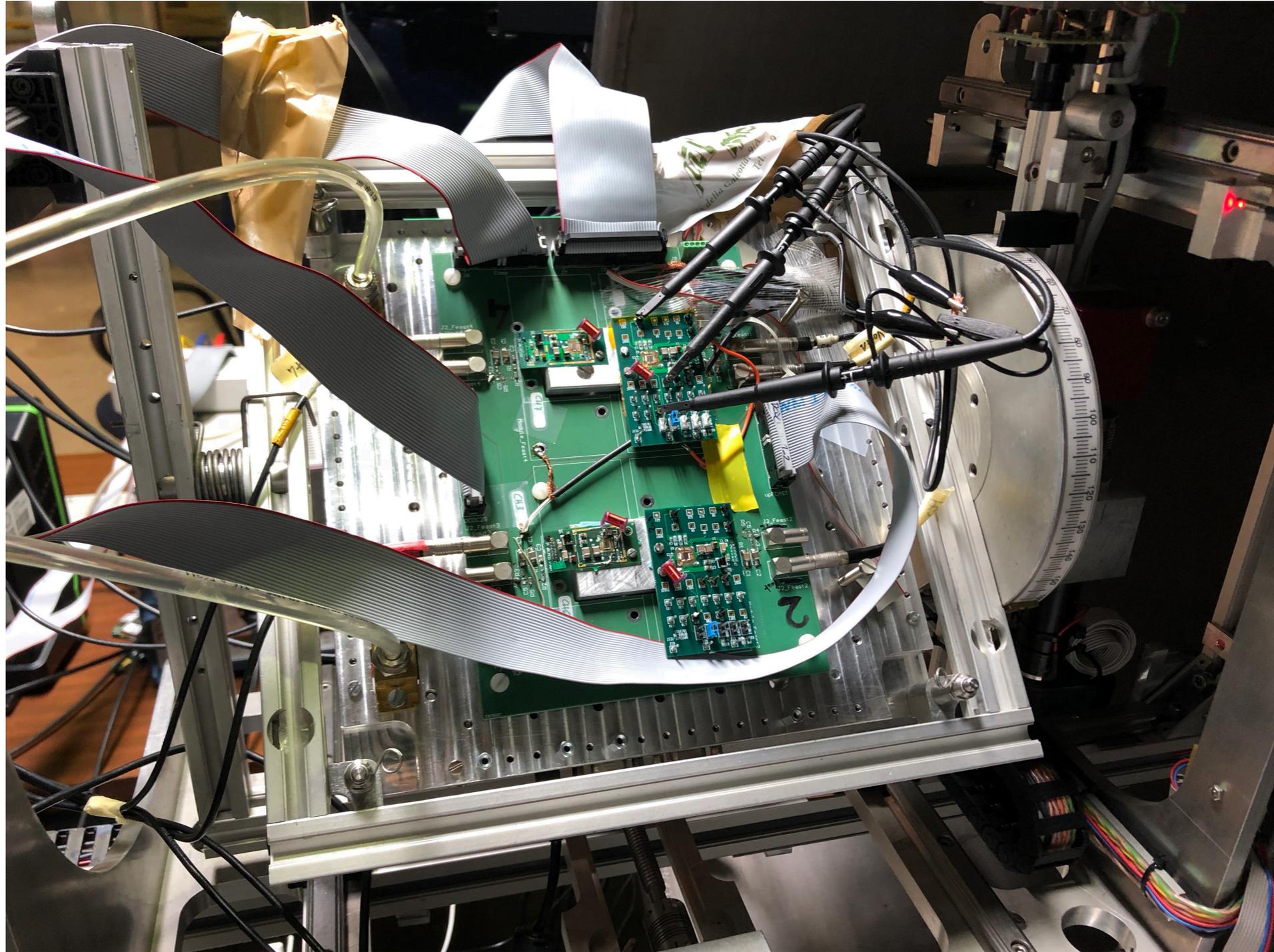
Stress tests with an ESD gun (1.2kV pulses) could produce somewhat similar damage - but the energy injected needs to be really large



An ESD gun is used to inject a discharge to the different pins of the FEAST2 package. To produce any damage, a visible spark has to be produced.

Radiation in ASIC?

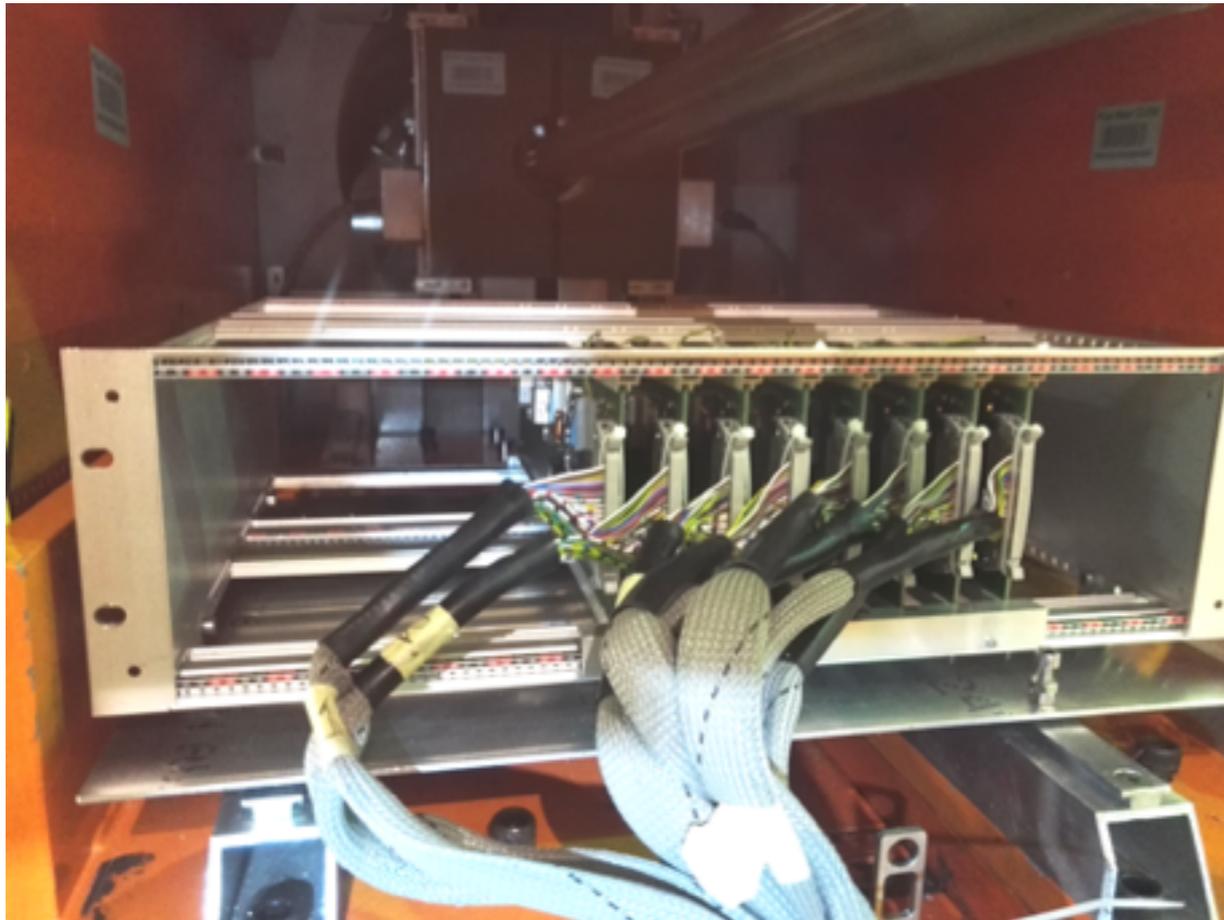
SEE Heavy Ion irradiation on samples pre-exposed to X-rays, Protons and Neutrons did not show any sign of damage



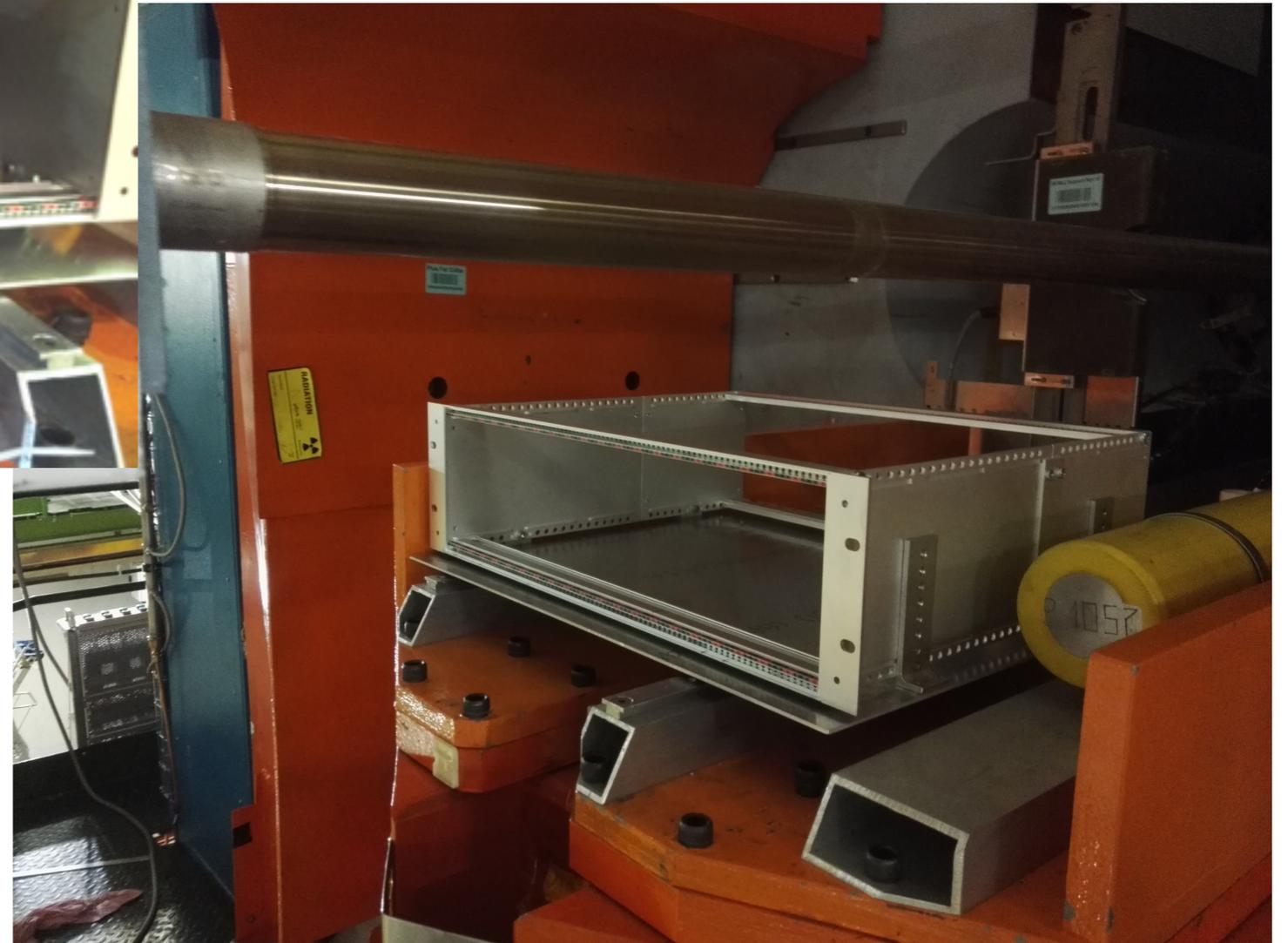
4 modules prepared on a motherboard are placed inside the irradiation chamber where they will be exposed to a Heavy Ion beam. The FEAST2 chips were previously irradiated with X-rays, 230MeV protons or neutrons from a reactor.

Radiation in ASIC? Environmental conditions?

Exposure of 32 FEAST2 in the CMS Castor Table was meant to reproduce some of the environmental conditions (proximity to the beam line, EM environment, radiation environment)



32 sample DCDC modules, both FEASTMP and CMS modules, are exposed and constantly monitored in the CMS Castor Table during the 2018 run.



Radiation in ASIC?

Environmental conditions?

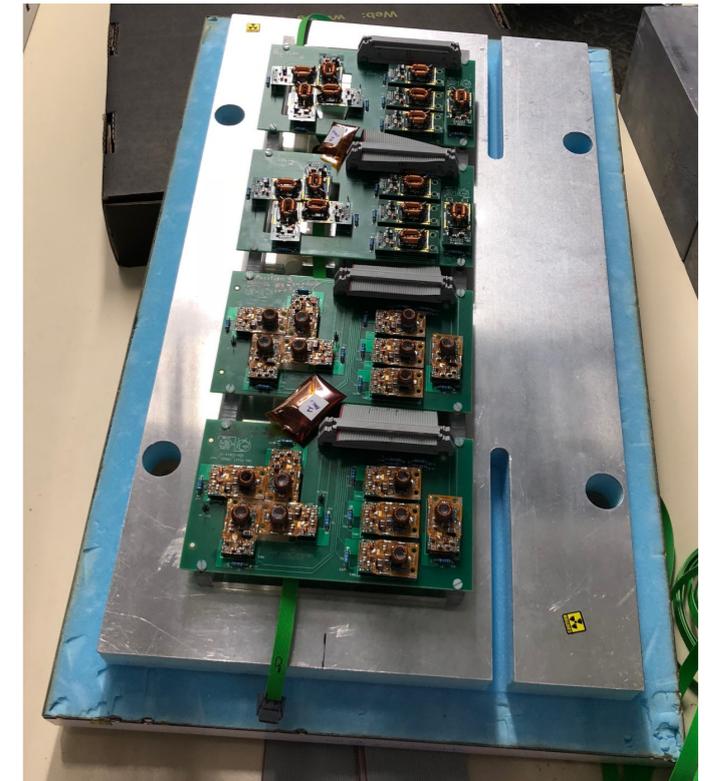
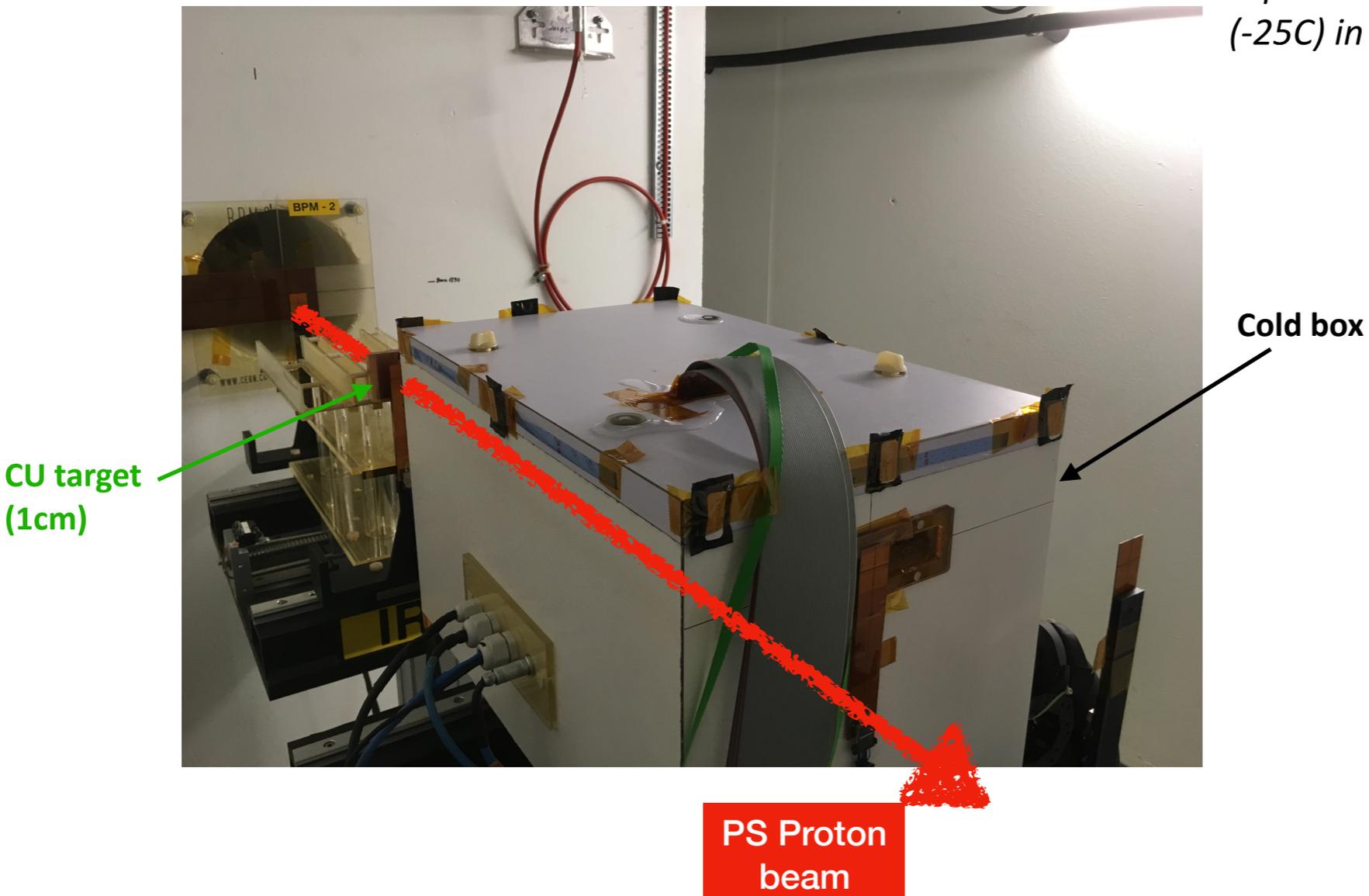
EM noise?

Two irradiation runs at the CERN IRRAD facility were instrumental in understanding the origin of the damage

Exposure of 32 FEAST2 at -25C at the CERN IRRAD facility

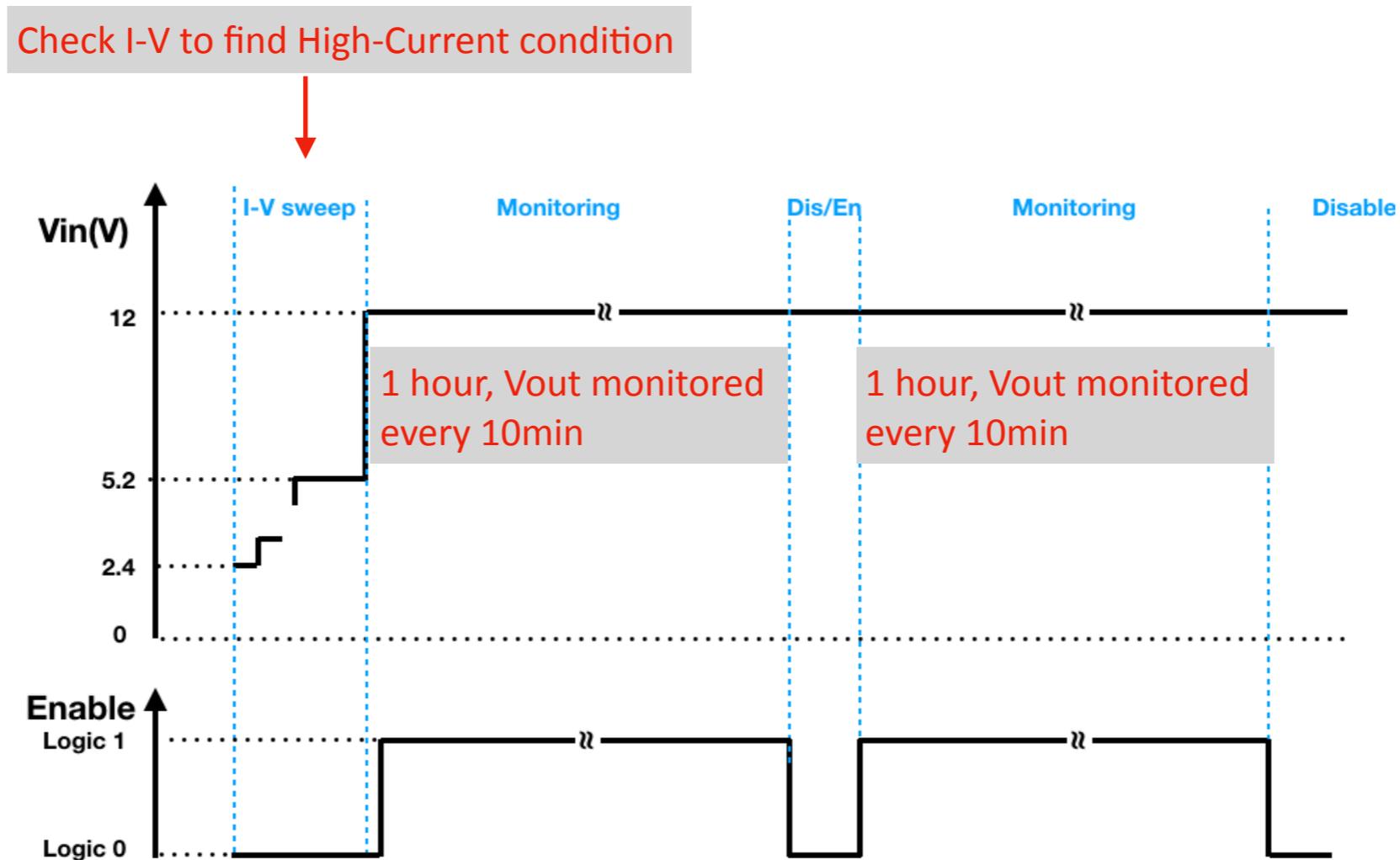
The facility run in a purposely modified configuration to expose the converters in a mixed field:
MANY THANKS to the IRRAD TEAM!

32 samples, both FEASTMP and CMS modules, are exposed and constantly monitored in a cold box (-25C) in the CERN IRRAD facility (May 2018).



32 modules inside the cold box

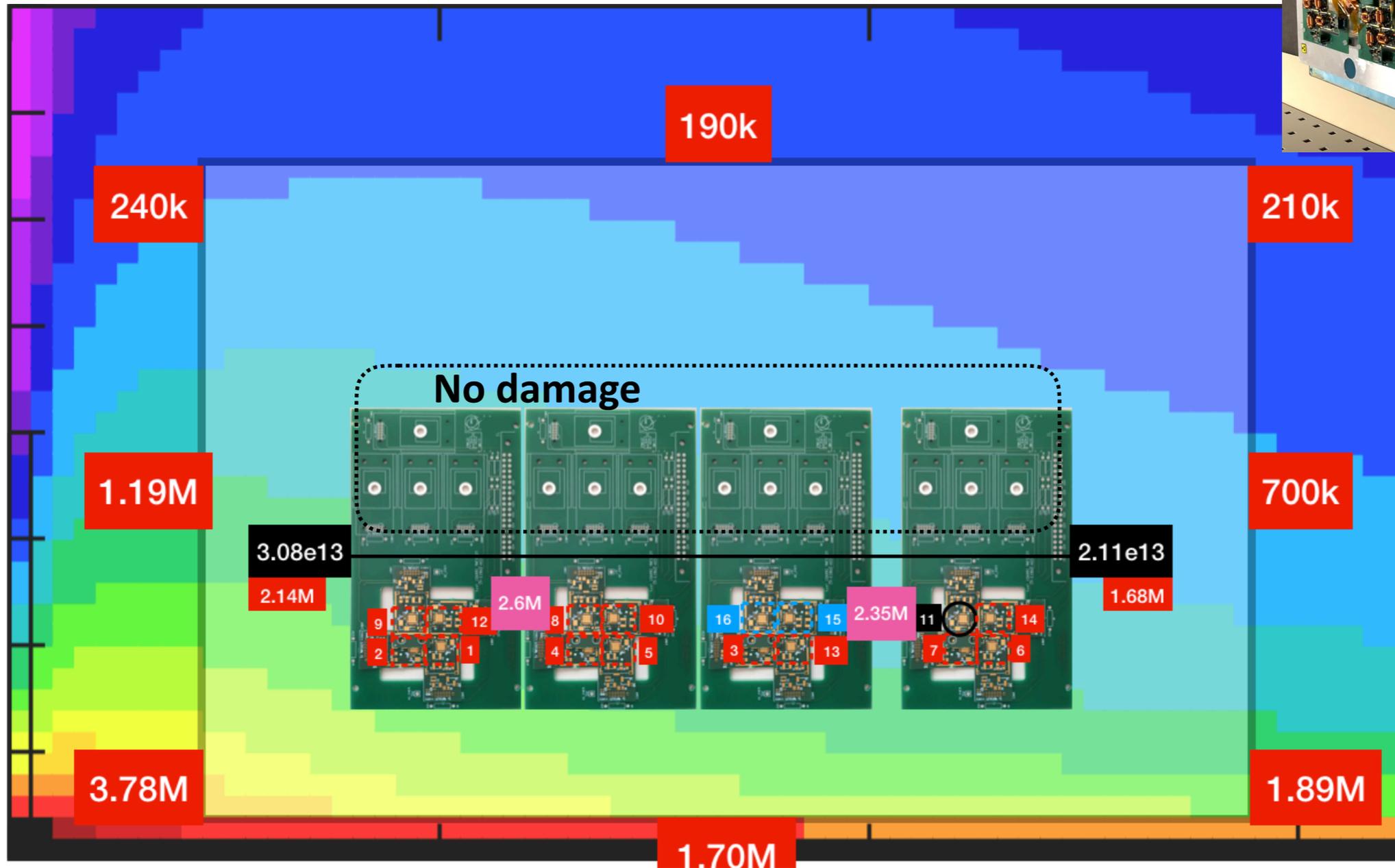
A specific bias and control sequence was used during the exposure



The full sequence lasts about 2 hours, with 97% of the time in “monitoring”

The results powerfully revealed some important correlation:

- **Between the damage and the integrated flux**
 - ▶ The first damage occurs after 9 days, then several samples per day
 - ▶ Only samples closer to the beam are damaged
 - ▶ Samples are damaged also after the end of the exposure
- **Between the occurrence of the damage and the disable-enable sequence**
 - ▶ Also true for the “High-Current”



Red = High-Current damage occurred during exposure

Blue = High-Current damage occurred after exposure

Black = failure

X-ray irradiation using the same enable/disable cycle as in IRRAD, and monitoring the current under UVLO thresholds, it was eventually possible to produce the same damage!

Now we had a tool to study the mechanism in detail!



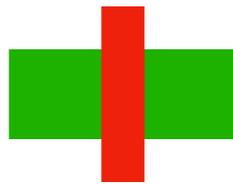
X-ray machine of the EP-ESE group

The crime reconstruction

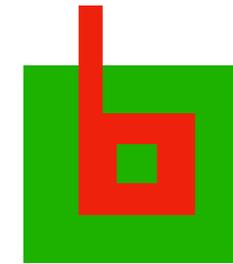


Radiation tests on the I3T80 nLDMOS transistor in 2008 revealed the impossibility to use Enclosed Layout Transistors (ELT): TID-induced leakage could not be avoided!

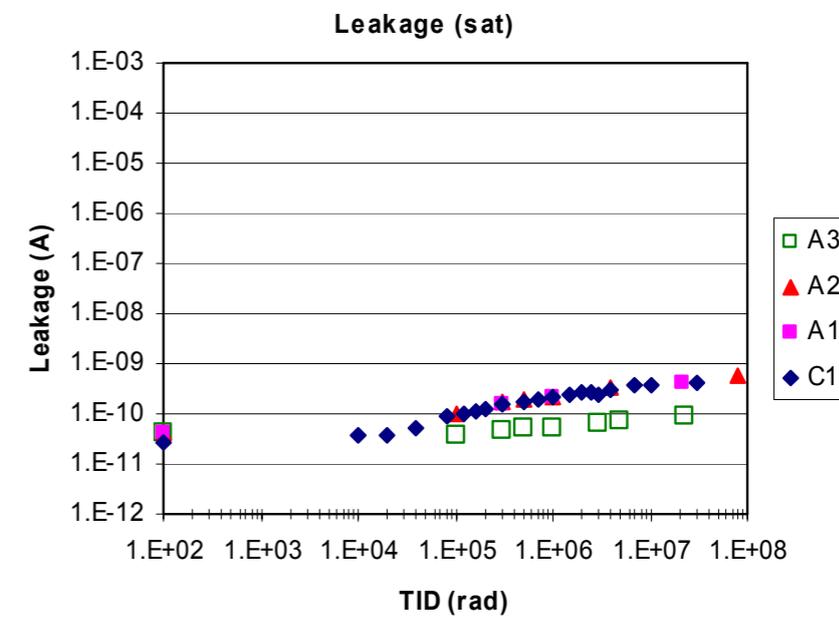
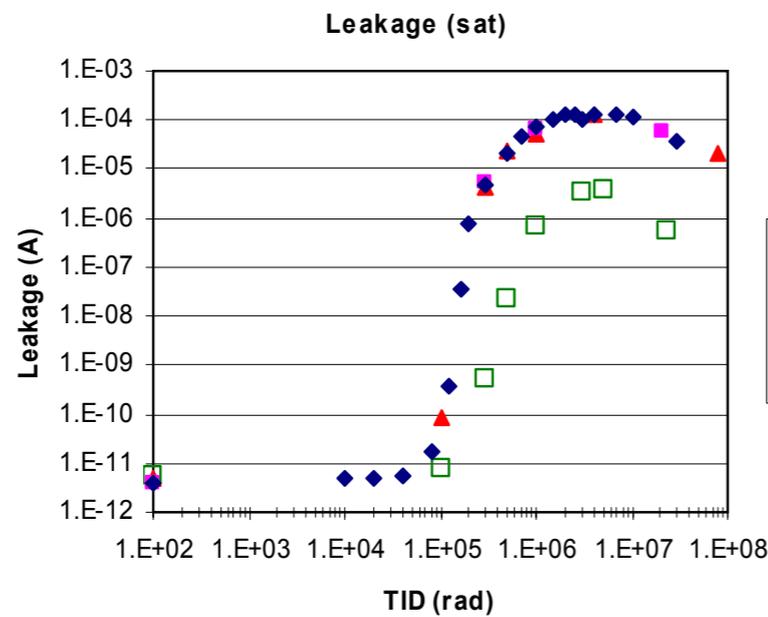
Linear layout



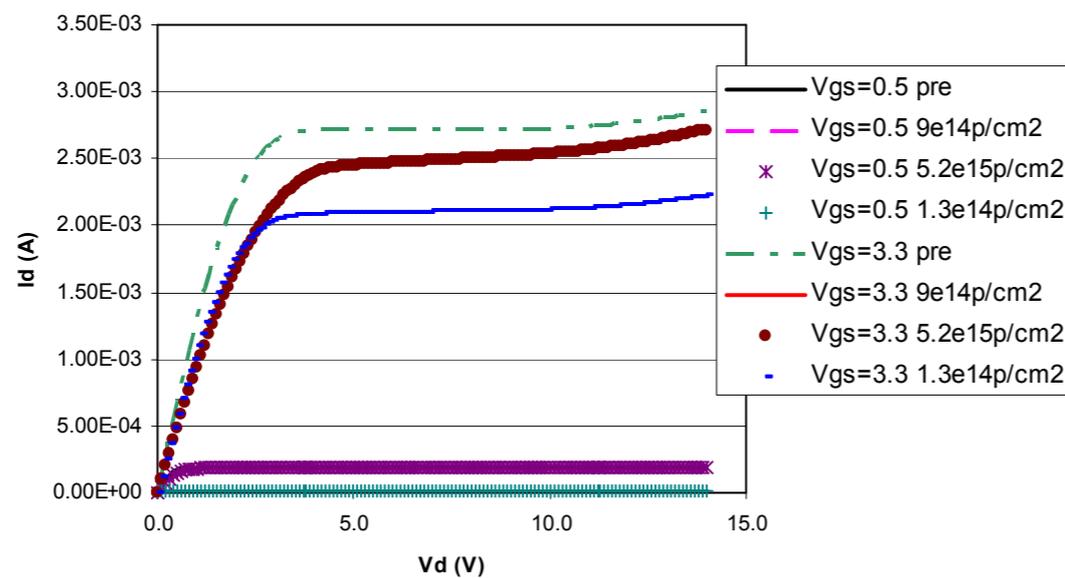
ELT



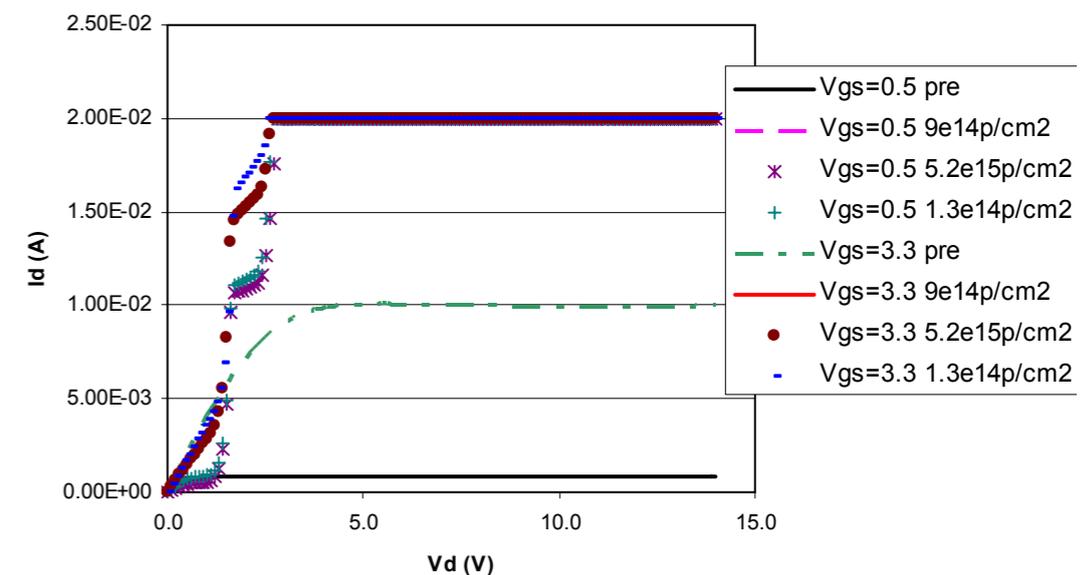
TID



$I_d=f(v_d)$ in linear scale

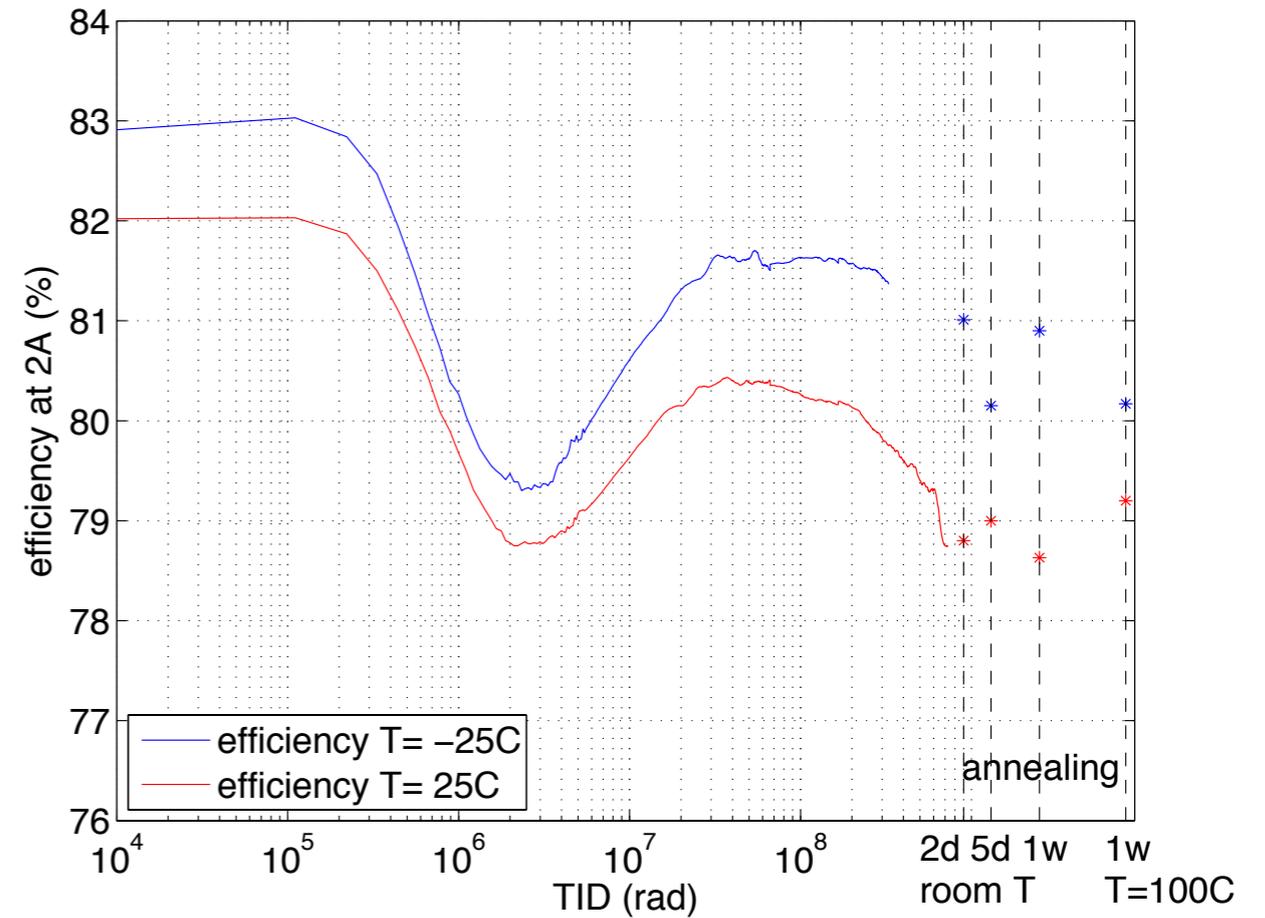
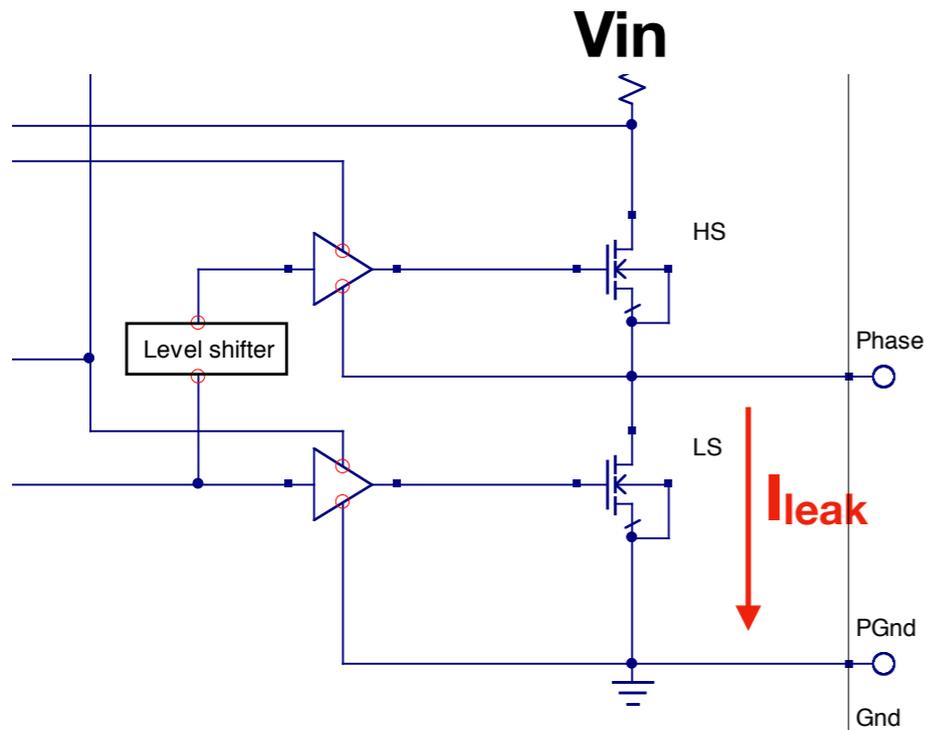


$I_d=f(v_d)$ in linear scale

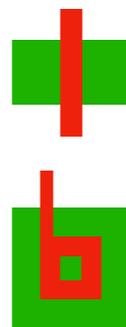


Displacement Damage

The leakage current in the nLDMOS transistors, used for the power train, induces an acceptable decrease in efficiency.



Elsewhere in the circuit, the leakage path is “cut” by adding core ELT transistors in series



Linear layout nLDMOS

ELT core nMOS

The qualification testing strategy of FEAST was based on:

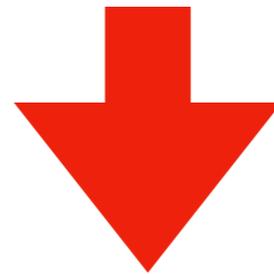
- the irradiation of the device to the maximum radiation levels**
- the verification on-line that the device was always functional (except for neutron tests, when the verification was done after irradiation)**
- periodic and/or final full characterisation of the main electrical parameters: efficiency, line and load regulation, thresholds (UVLO, enable, OCP, OTP)**

- ✓ X-rays for TID up to 700Mrad**
- ✓ Heavy Ions for SEEs**
- ✓ Pulsed laser test for SEEs**
- ✓ Neutrons from a reactor for displacement damage**
- ✓ 230MeV protons for SEEs (+ TID + DD)**

Somewhere else, in another continent, the TBM chip for the CMS pixel system was being designed

During a late and quick addition of functionality, logic unprotected from SEUs was integrated in the final chip

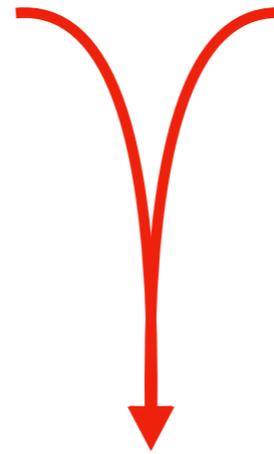
A reset command was not implemented



In a severe radiation environment the correct functionality is frequently corrupted, and a power cycle is needed to re-initialise the chip

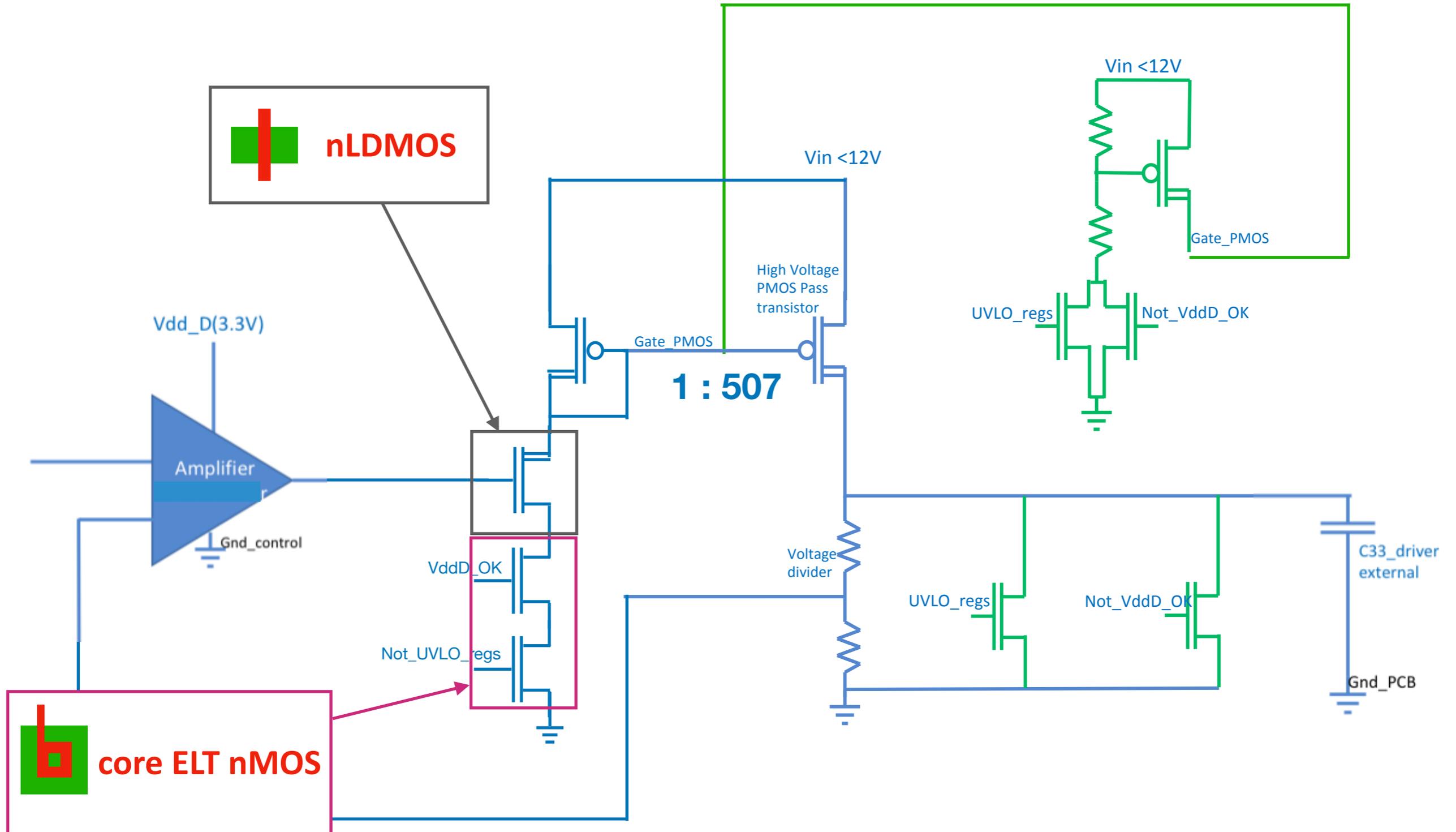
Potentially “leaking” nLDMOS in FEAST

Unprotected logic and no reset in TBM



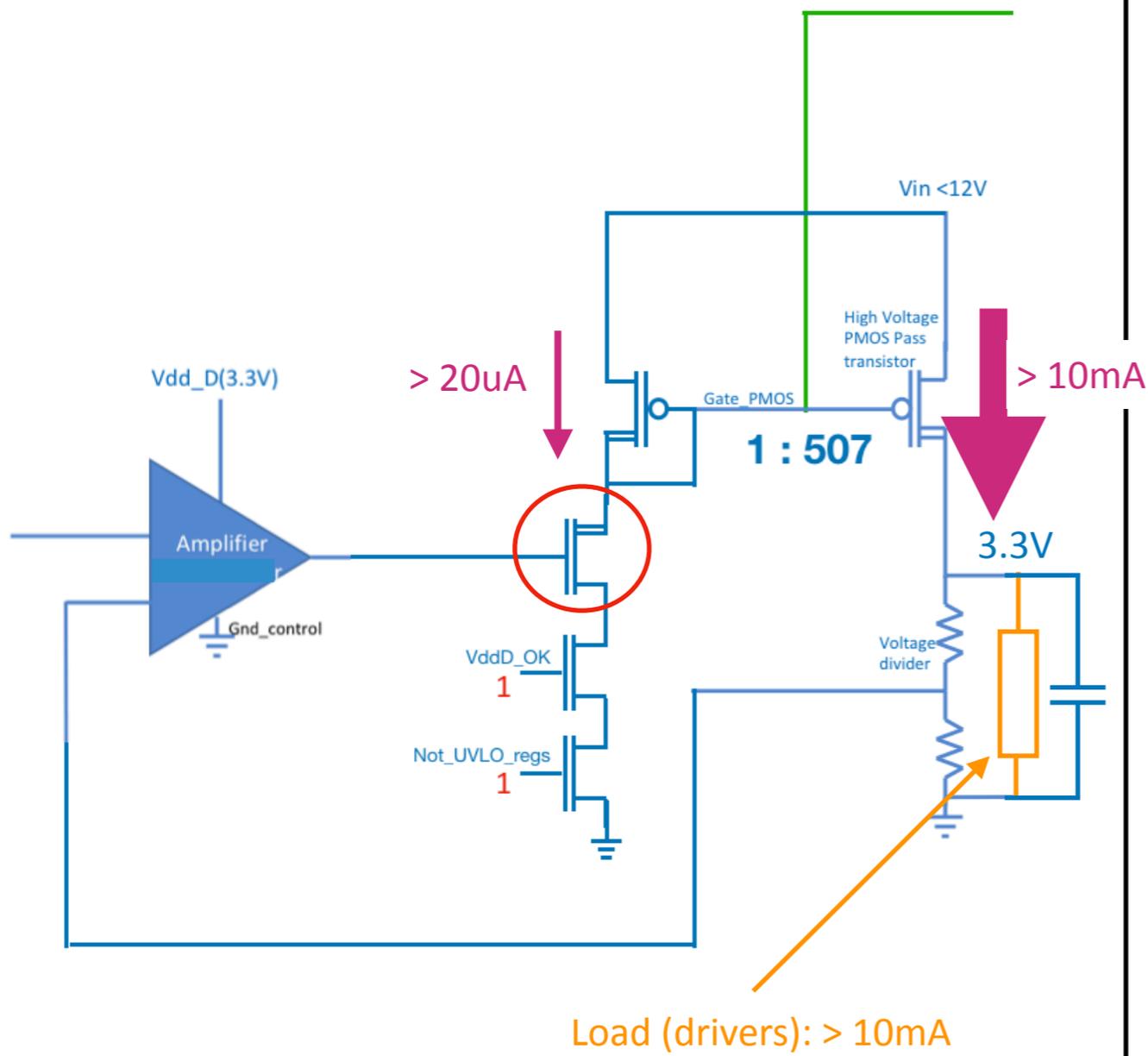
Failure of FEAST2 in the CMS pixel system during the 2017 run

The problem is localised in the linear regulator (V33Dr) that provides the required current to the drivers of the power transistors (HS and LS)

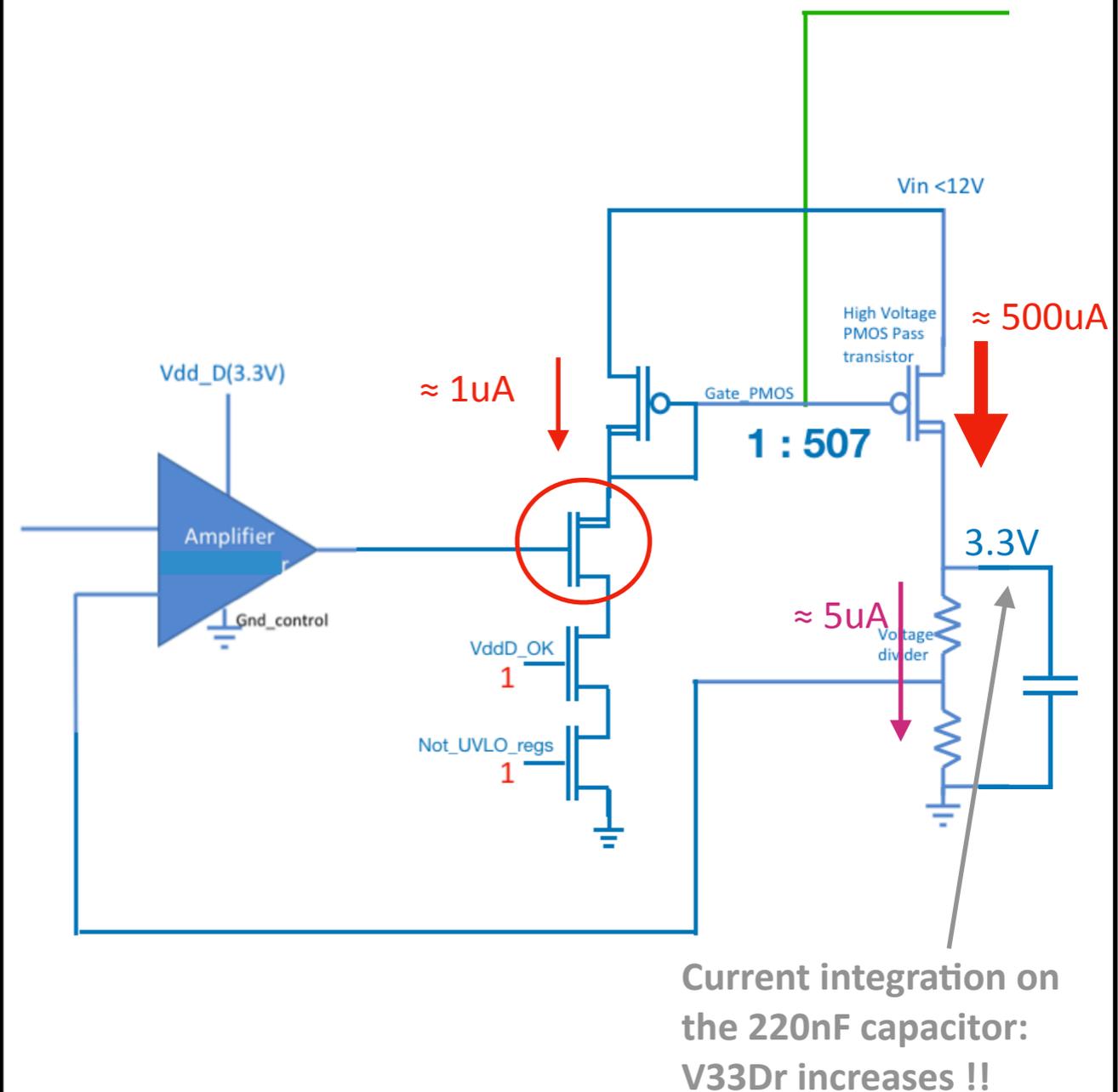


In the presence of a large TID-induced leakage in the nLDMOS, consequences appear **ONLY** when FEAST2 is disabled (no load for the V33Dr regulator)

“enabled”

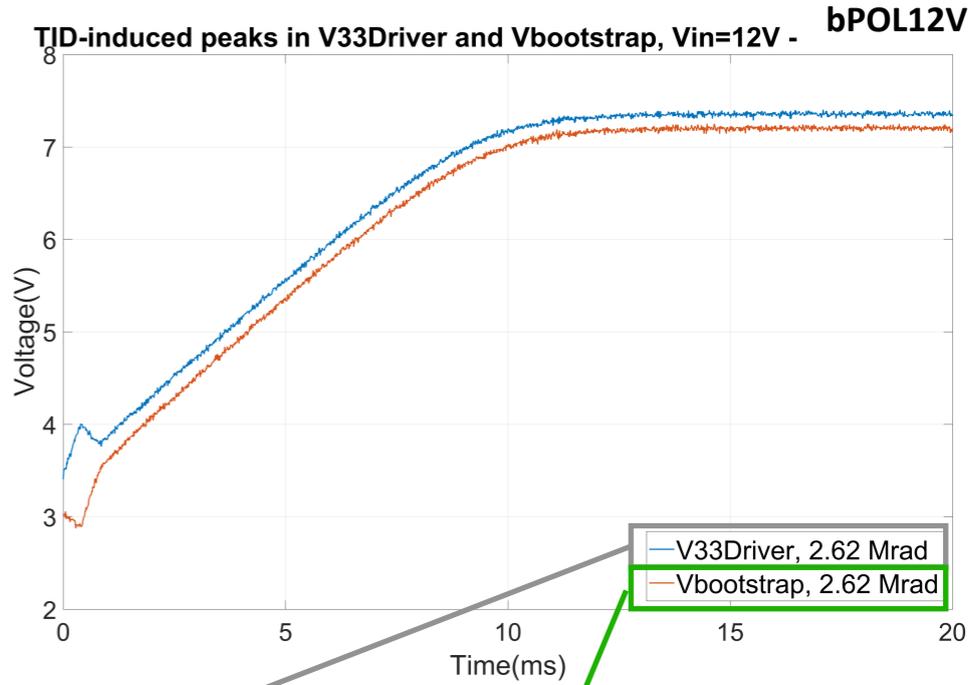
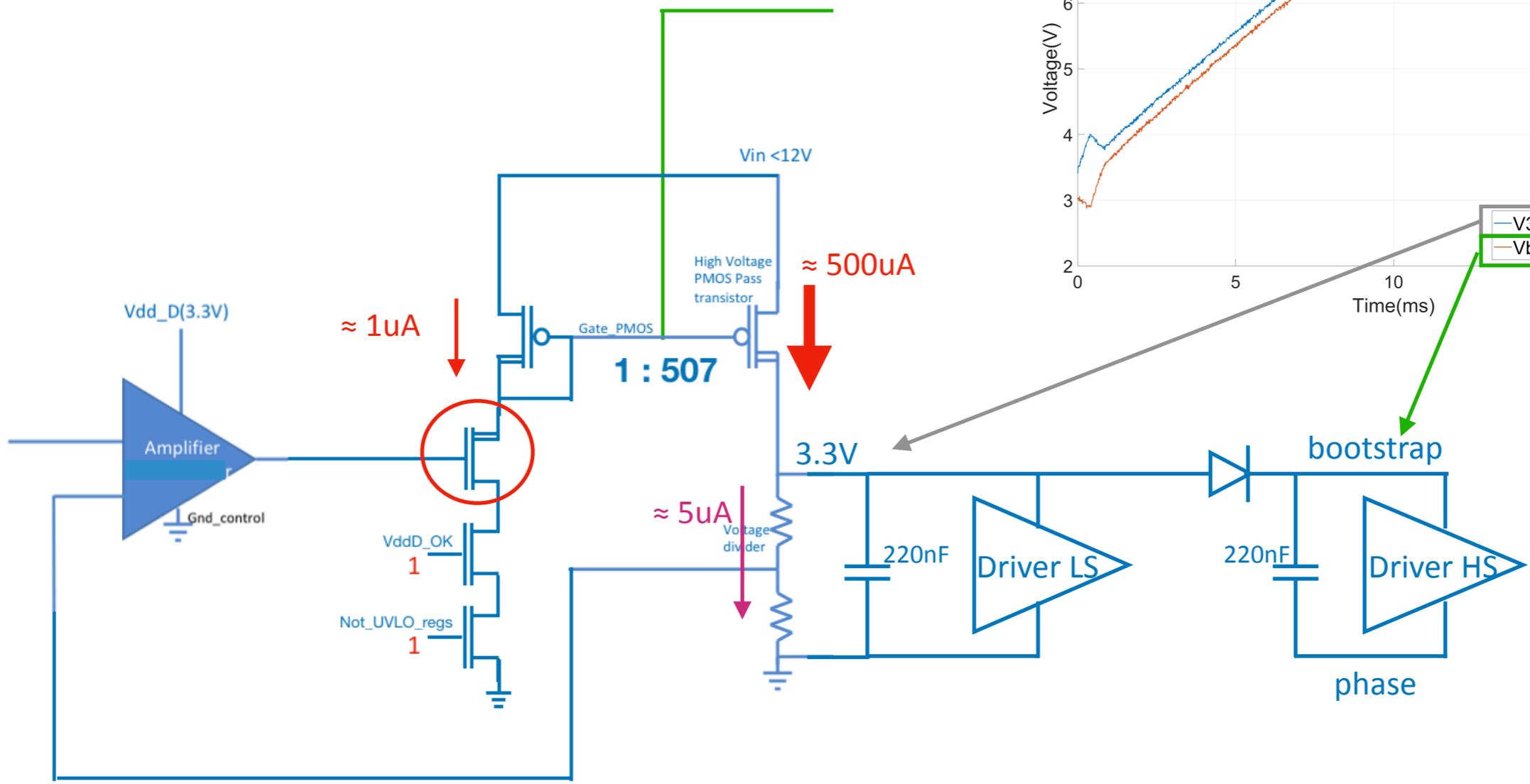


“disabled”



The integration of the current on the two 220nF capacitors has eventually been observed experimentally in June 2018 on samples exposed to TID at our X-ray facility

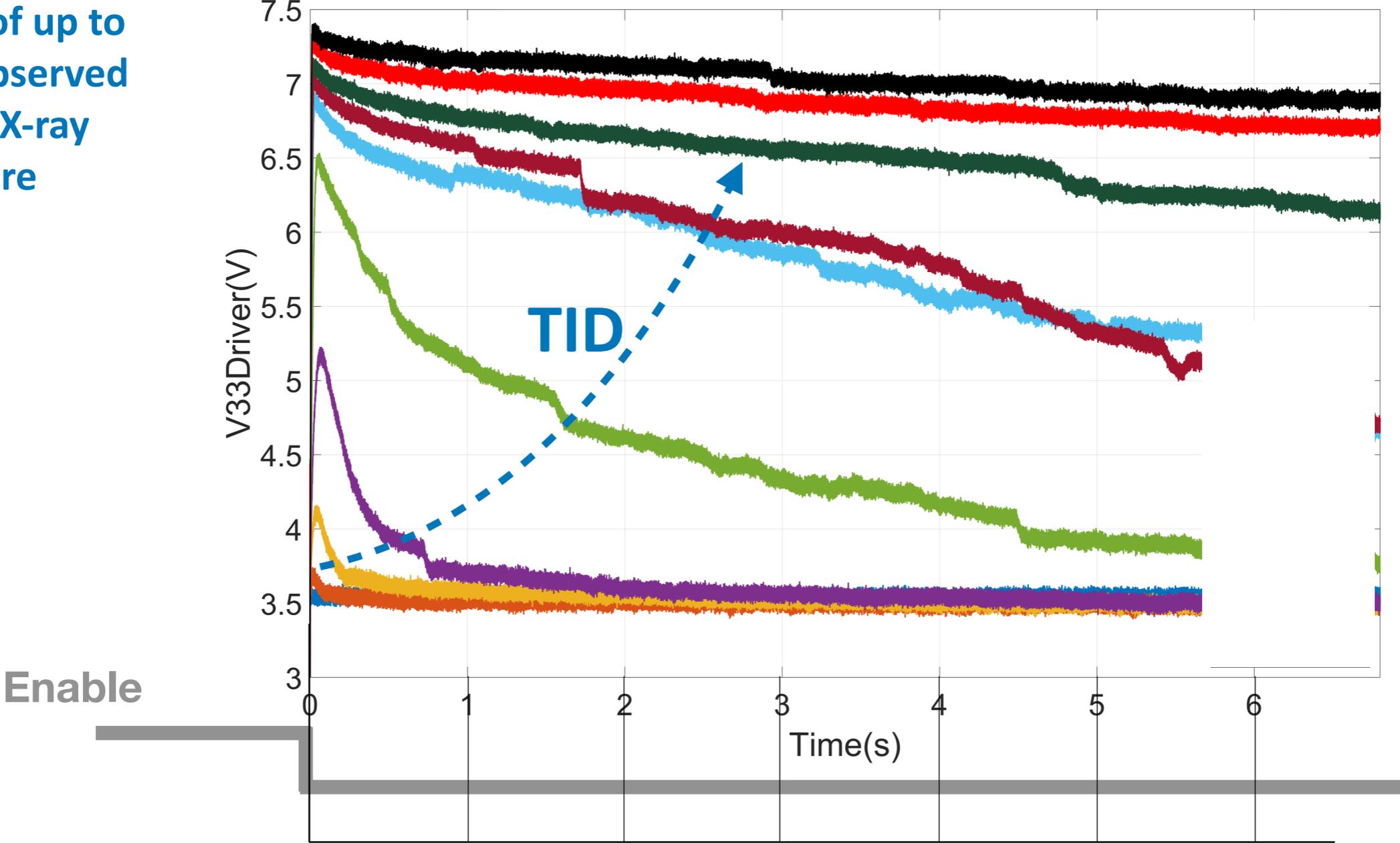
“disabled”



We observed a “voltage peak” on the V33Dr node when FEAST2 is disabled during X-ray exposures. The voltage peak increases with TID

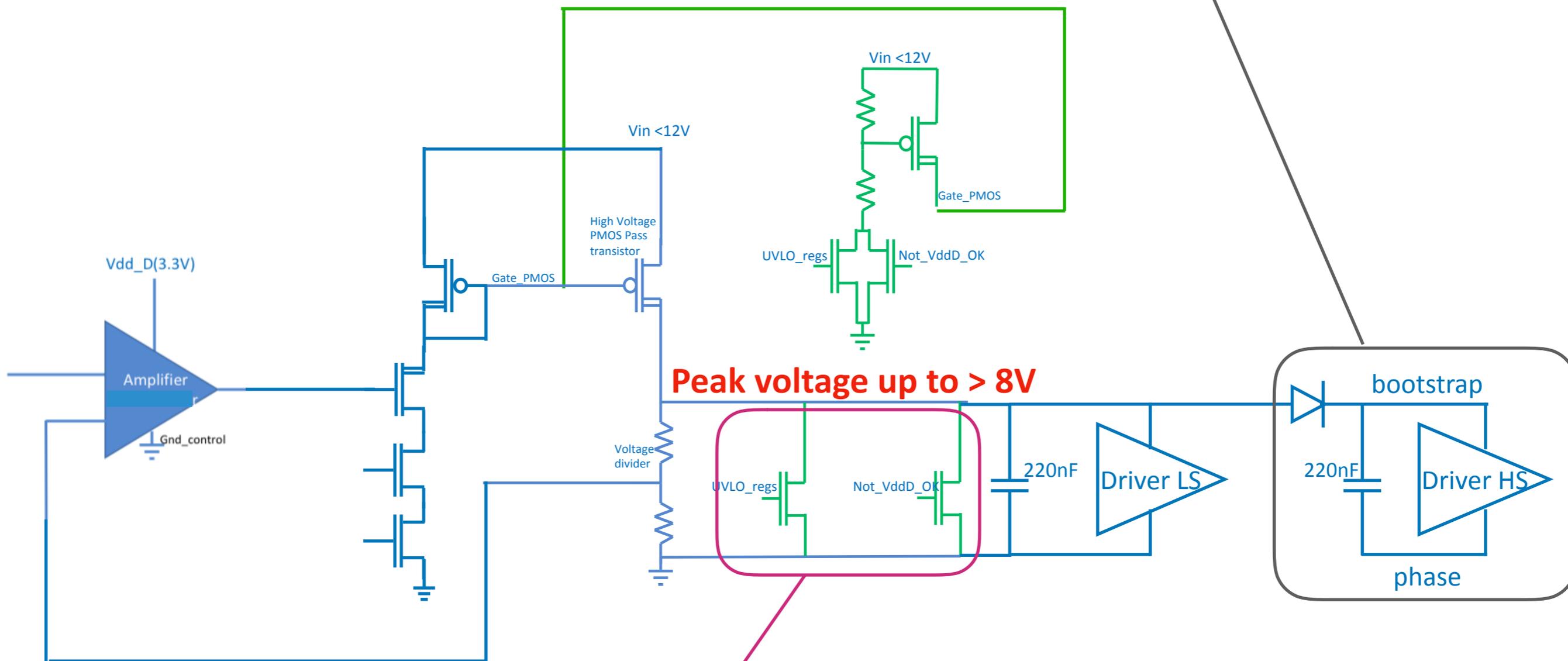
Peaks of up to 8.5V observed during X-ray exposure

Example waveforms at the V33Dr node



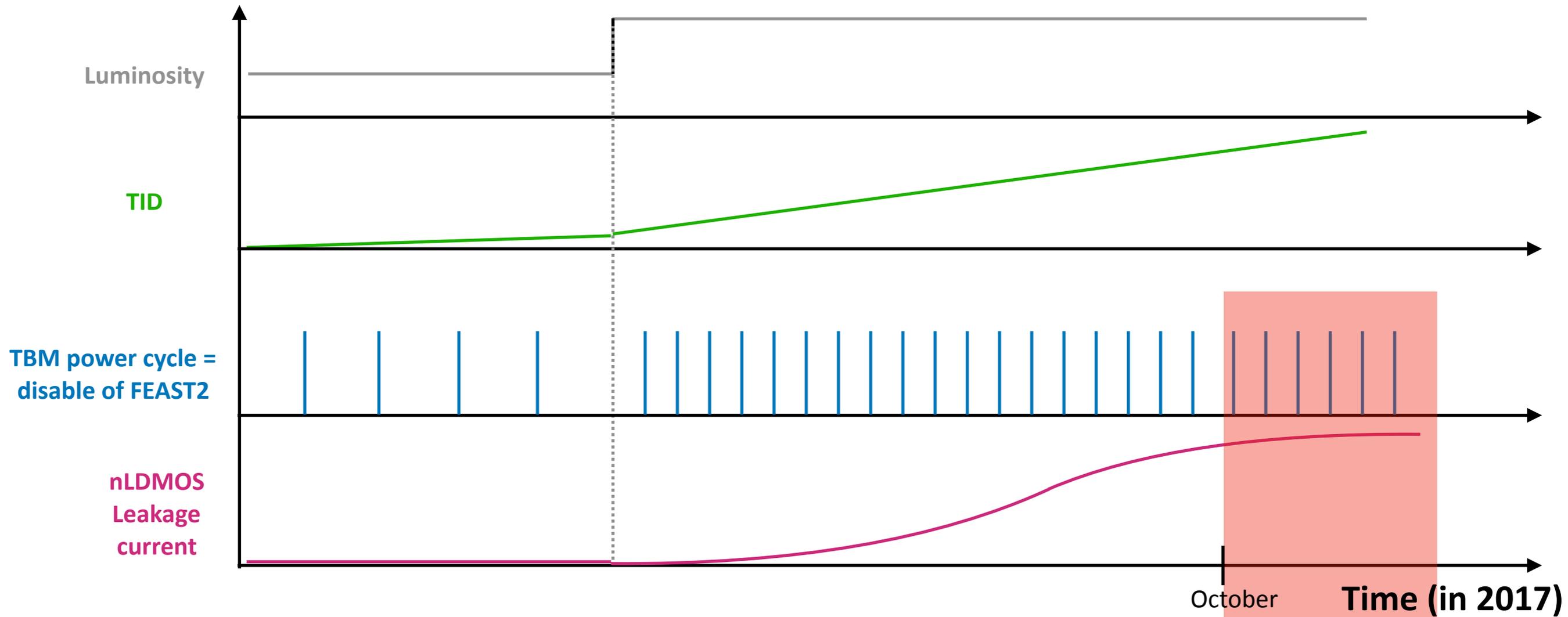
The voltage at the V33Dr node goes well beyond the nominal maximum of 3.3V+10%. This voltage stress might end up damaging a device. We have observed 2 damage mechanisms, and Failure Analysis with emission microscopy and OBIRCH have confirmed the current paths.

If a device along this path is damaged => increase in regulator current => FEAST2 continues to operate



If a clamp transistor is damaged => linear regulator stuck => FEAST2 failure

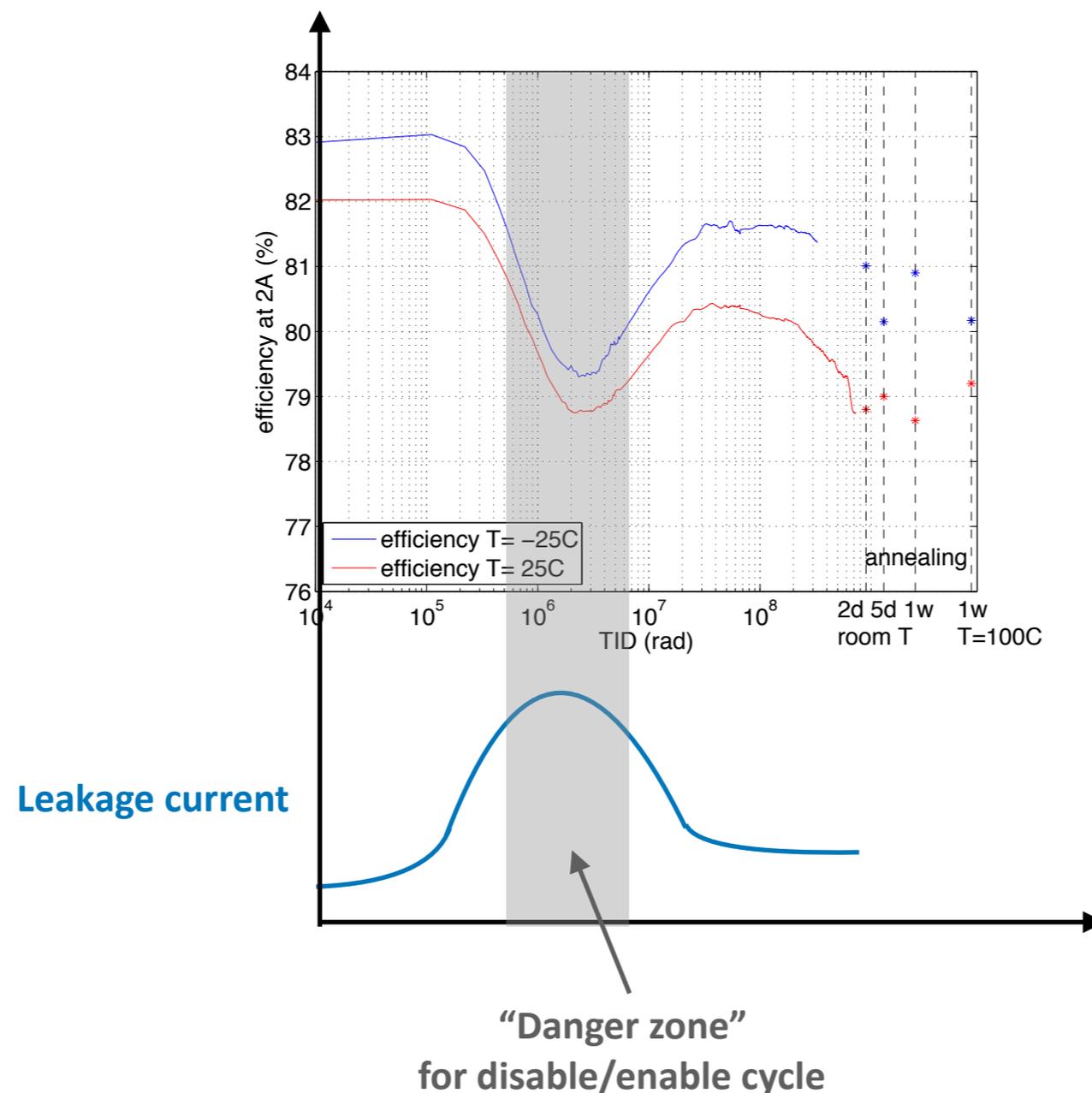
A graphical representation of the narrative



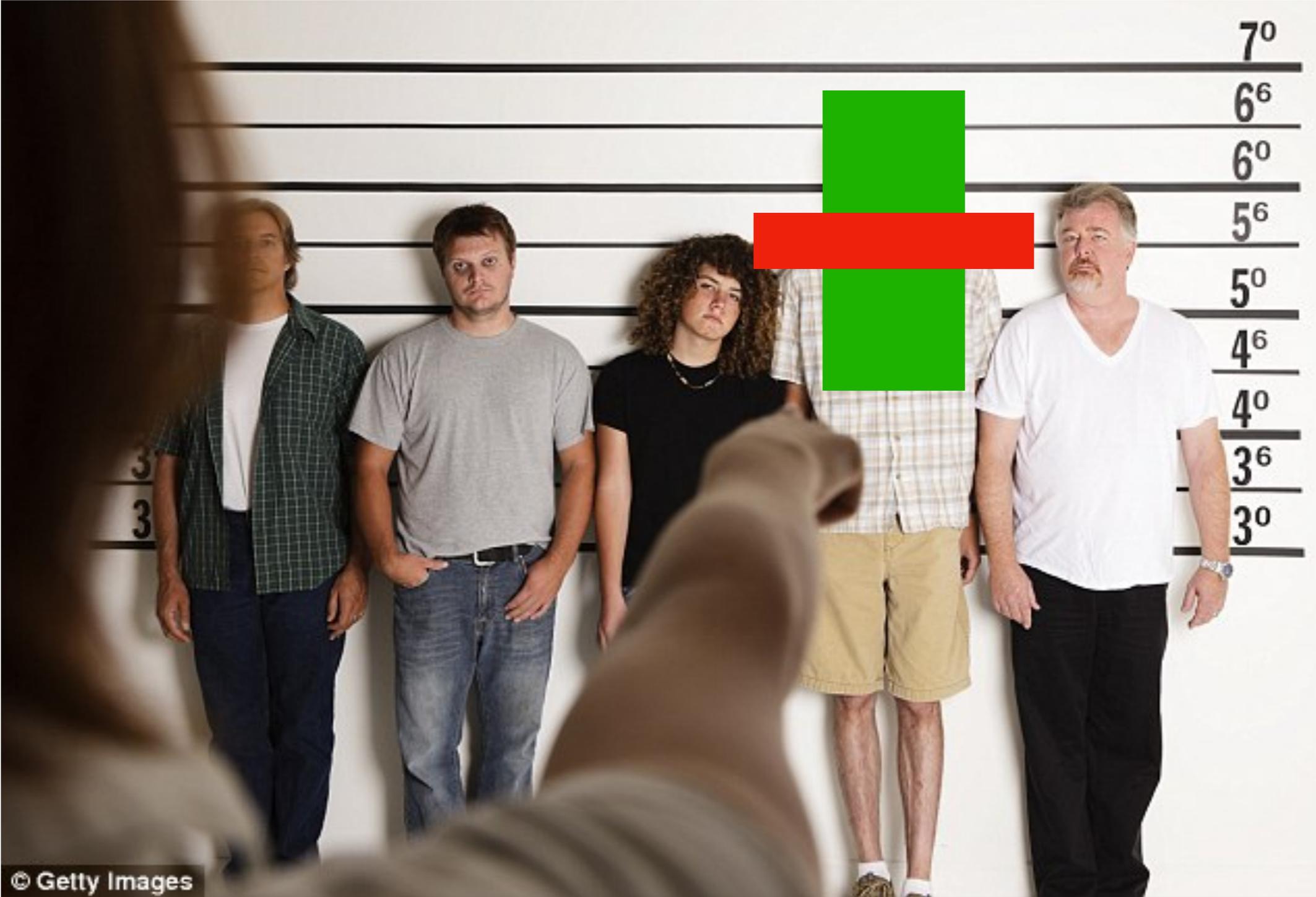
TBM requires a power cycle
=> FEAST2 is disabled while the leakage is large
=> peak voltage at V33Dr
=> damage

This model for the damage explains why the problem was not observed during the radiation qualification of the FEAST2 ASIC

1. To produce the damage, it is necessary to perform disable/enable cycles at the time when the TID-induced leakage is large
2. To observe the signature of the damage, in the vast majority of the cases (High-current), it is necessary to measure the current consumption below UVLO thresholds



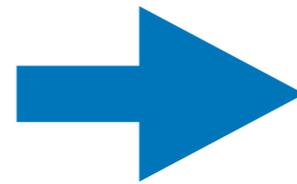
The perpetrator



Patches and long-term solutions

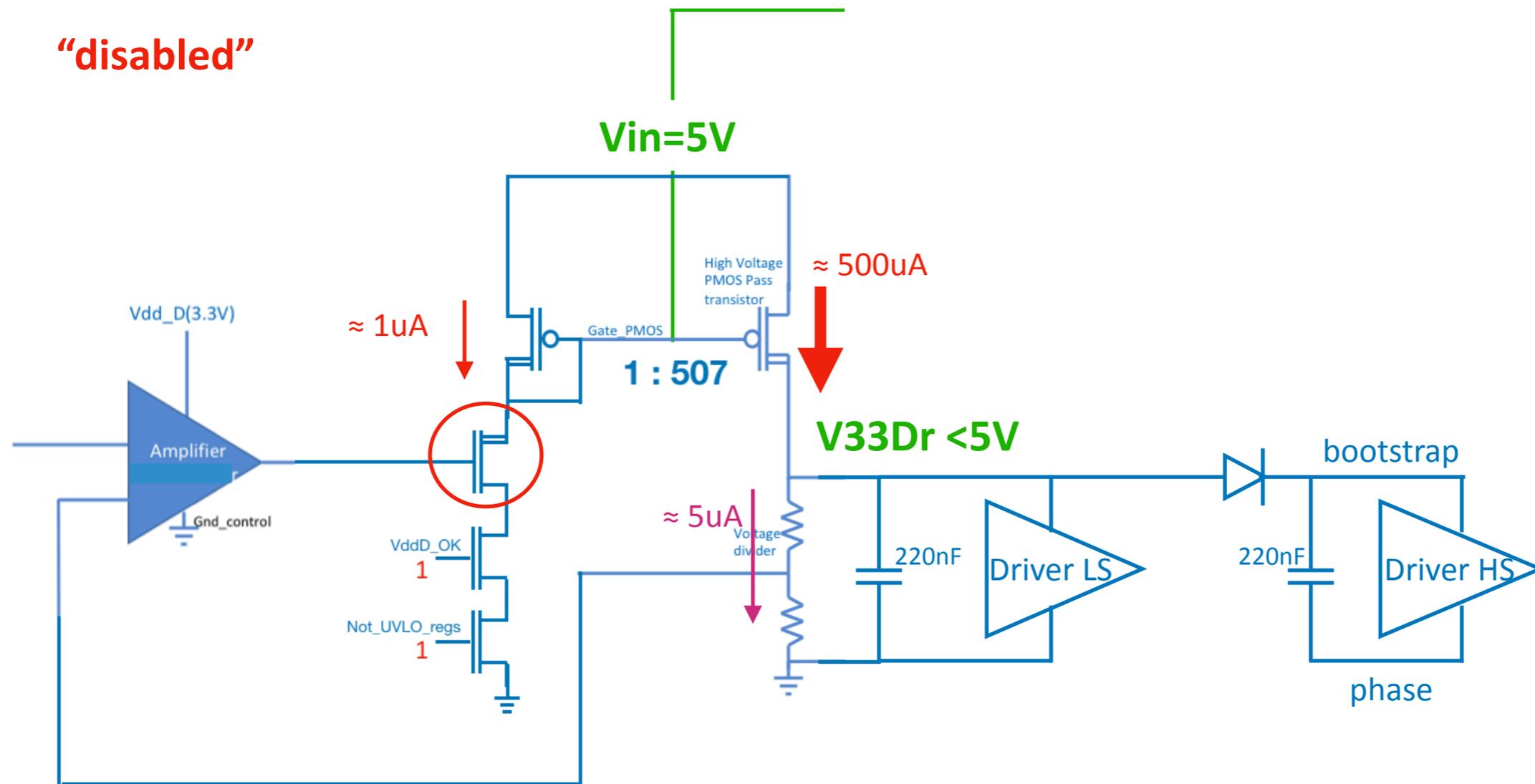
Patch 1 for FEAST2.1 (only for environments with TID > 500krad):

The voltage peak can get close to V_{in} , but not higher



Disable the converter at lower V_{in}

“disabled”

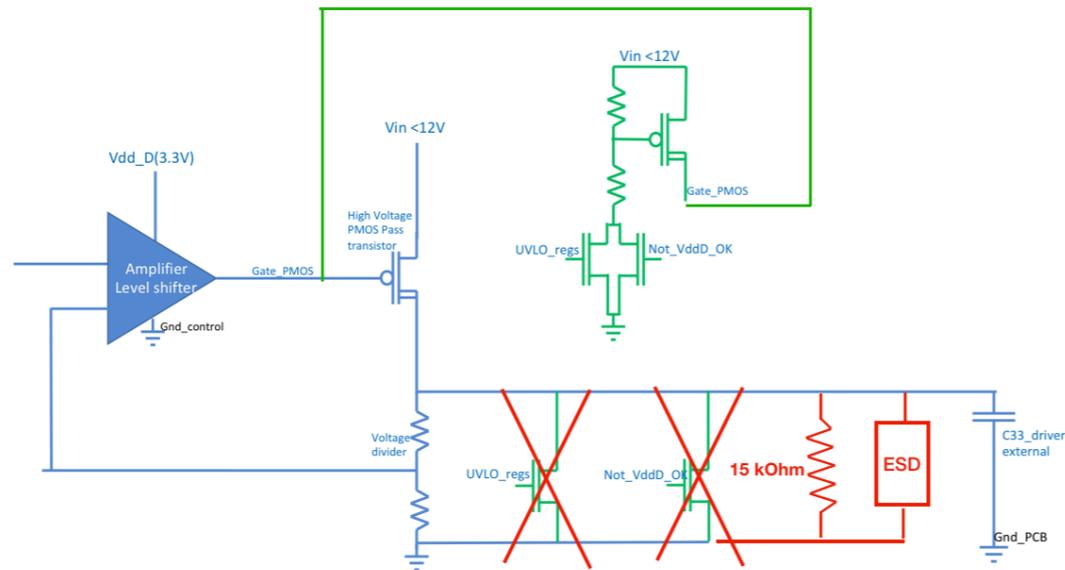


In case of a power cycle (V_{in} down to 0V), the converter is disabled by the UVLO at about 4.4V

This strategy was successfully used during the full 2018 run of the CMS pixel detector, and its efficiency was demonstrated in the second IRRAD run and in X-ray testing

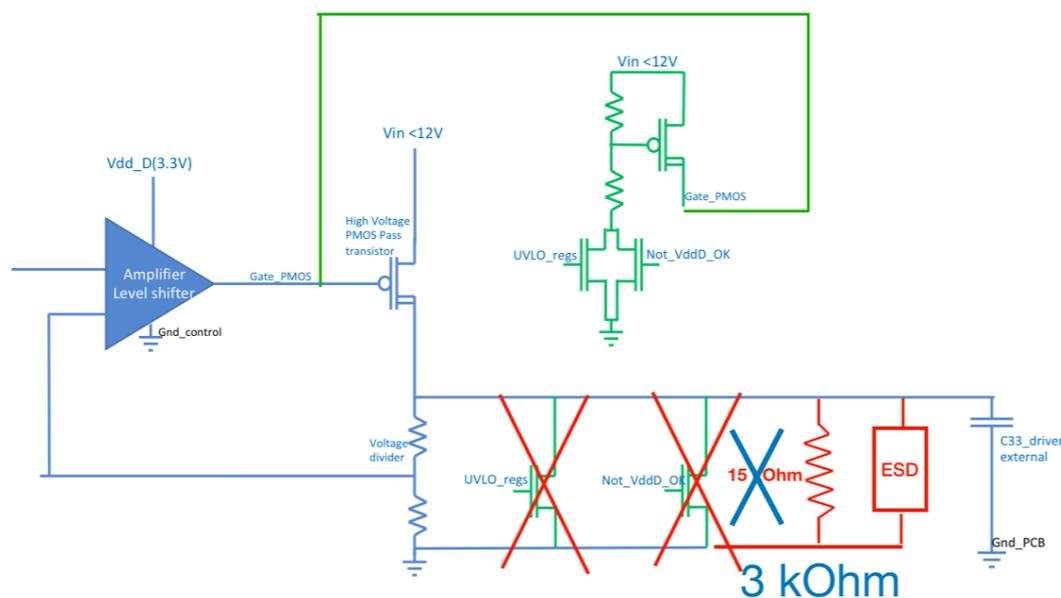
Long-term solutions:

FEAST2.2



Used in FEASTMP modules produced in the first half of 2019. During X-rays testing, no voltage peak on V33Dr event at -30°C if the dose rate is below 180krad/hour

FEAST2.3

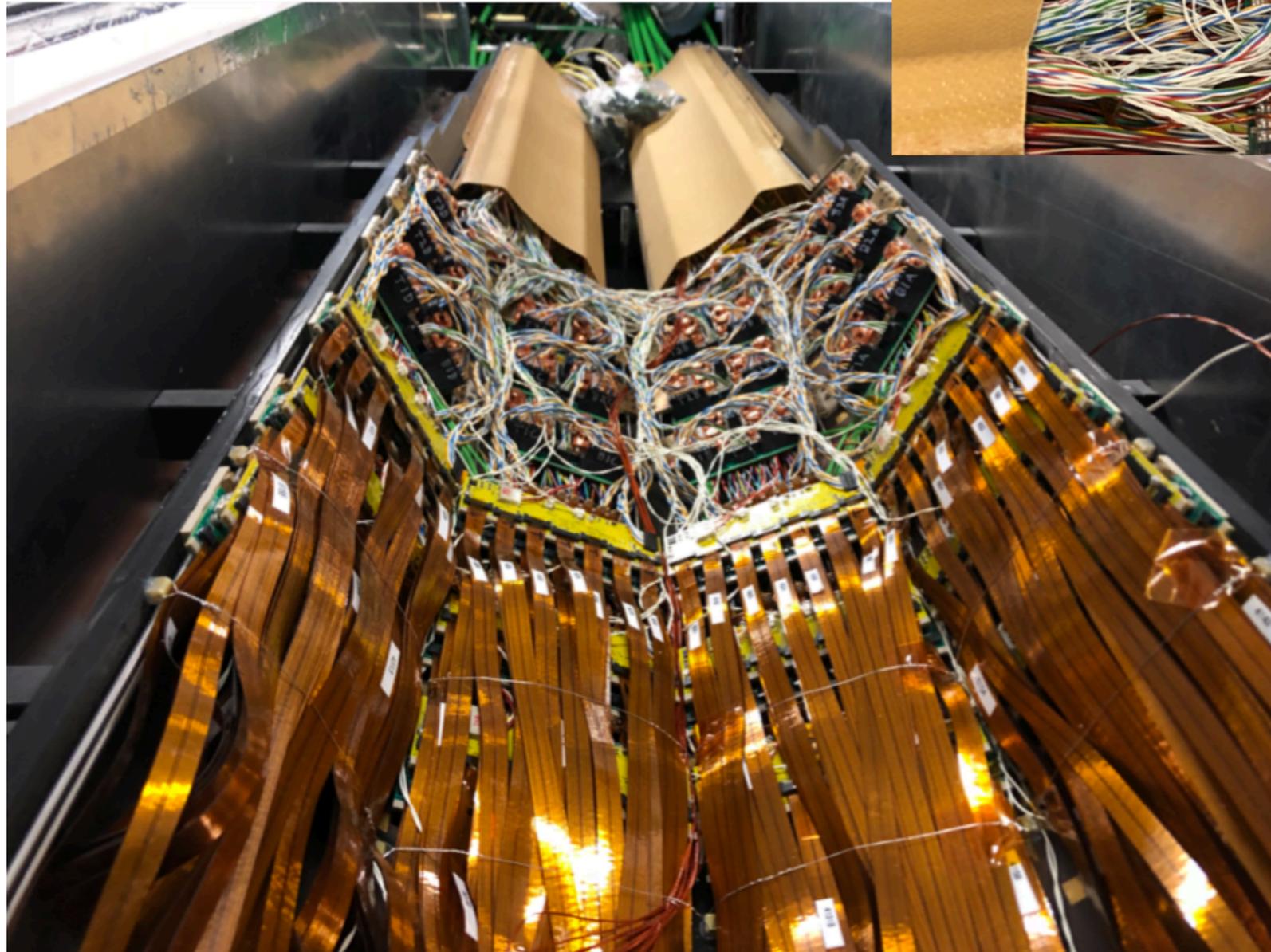
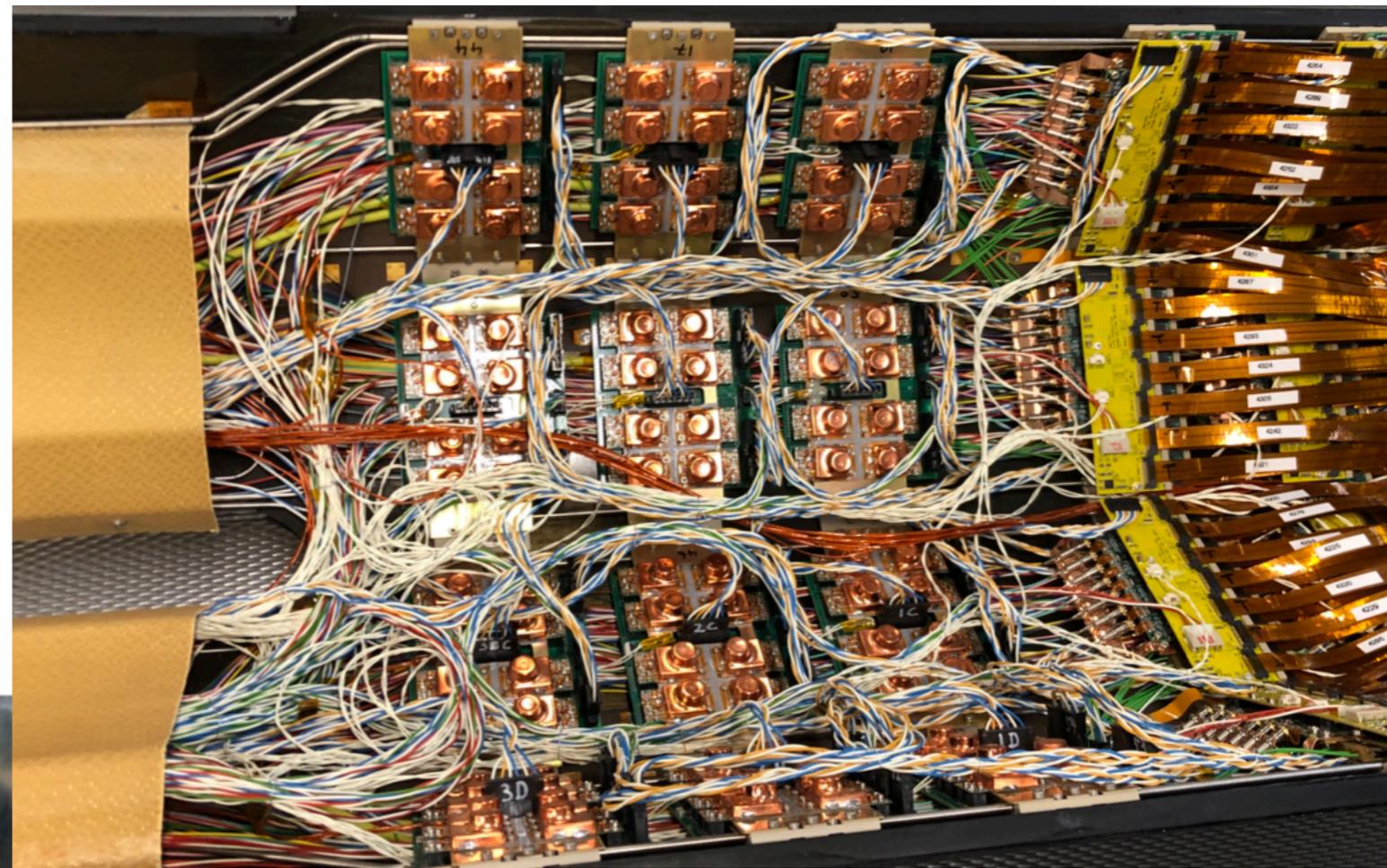


Present default version for all modules

Final thoughts

This is a very complex system

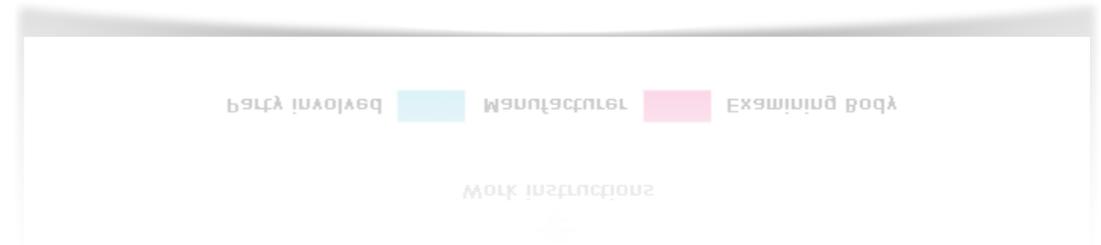
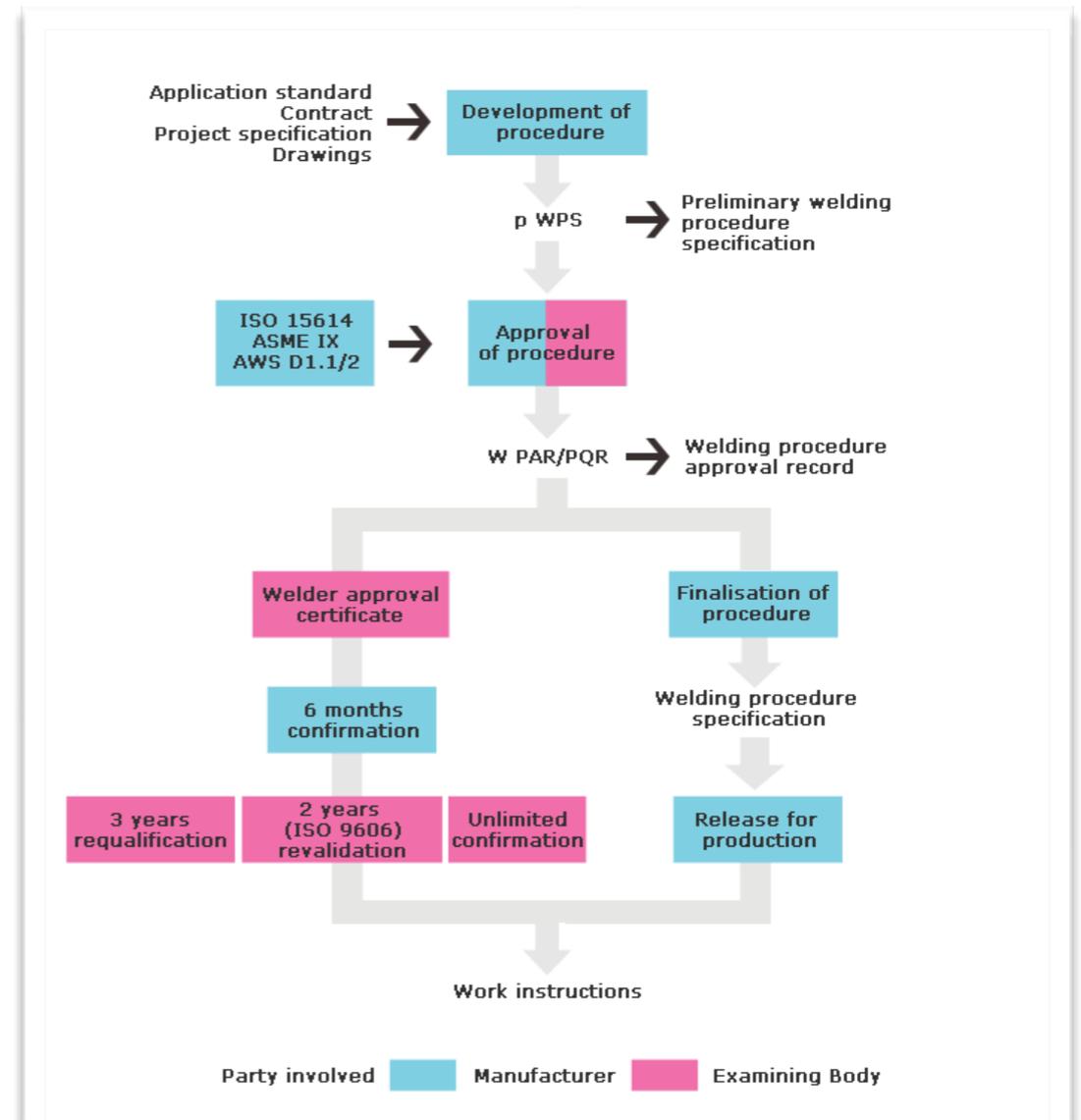
- Assembly of different sub-systems
- Unique “prototype”
- Tested in the real environment only



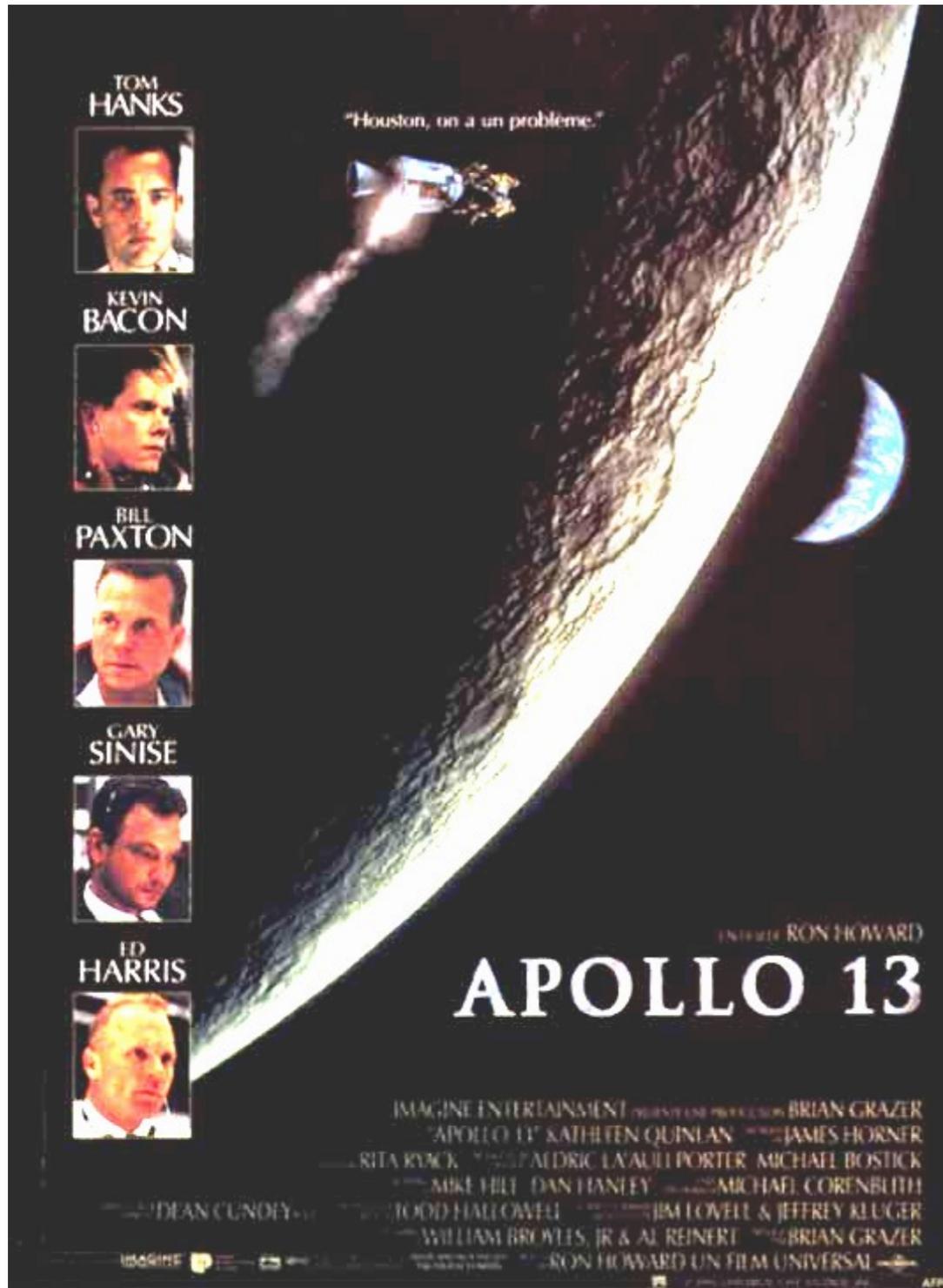
List of expert EMC recommendations after the observation of the system:

- **Improve filters for incoming transients on the DC supply lines**
- **Improve capability of system to route high frequency common mode (including connection of cable screens)**
- **Improve system equipotentiality (including cable screens, glued screens of detector and metallic parts of the cooling circuits)**
- **Avoid using twisted pairs for asymmetric signal or power connection**
- **Avoid separated grounds leading to severe lack of immunity against E-fields and transient H-fields**

How about qualification practices?



We are not NASA in the 1970s...



Some reasons to be grateful for our luck

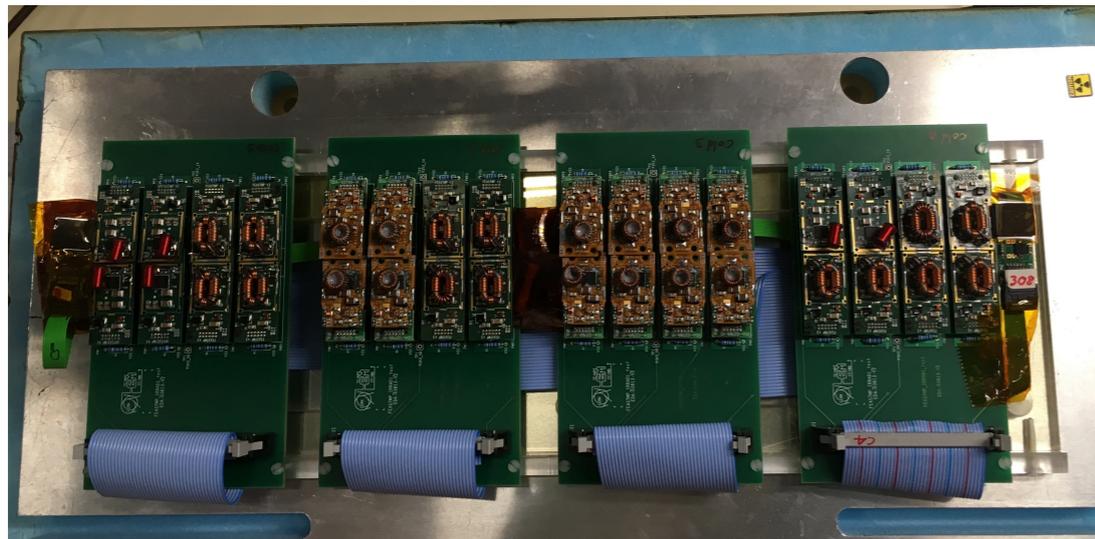
- **The designers of the failing component were still around, and at CERN**
- **The problem happened to a detector that is amongst the easier to open**
- **Once understood, patches and fixes were easy to implement**
- **The problem appeared in 2017 and not in HL-LHC trackers**

**Personally I'm always ready to learn,
although I do not always like being taught**

W. Churchill

**Experimental confirmation:
Second run at the IRRAD facility**

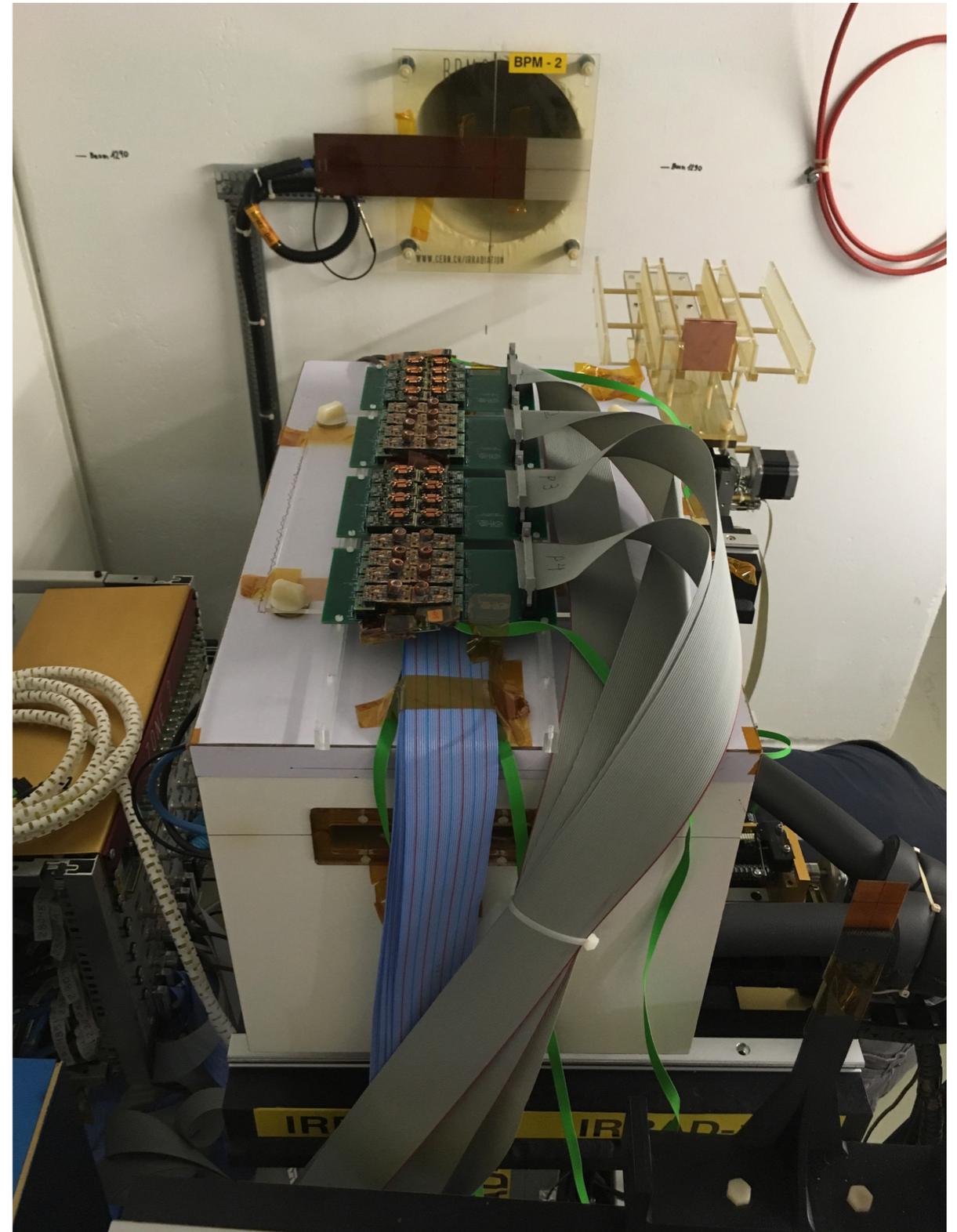
A second run in IRRAD used 64 converters



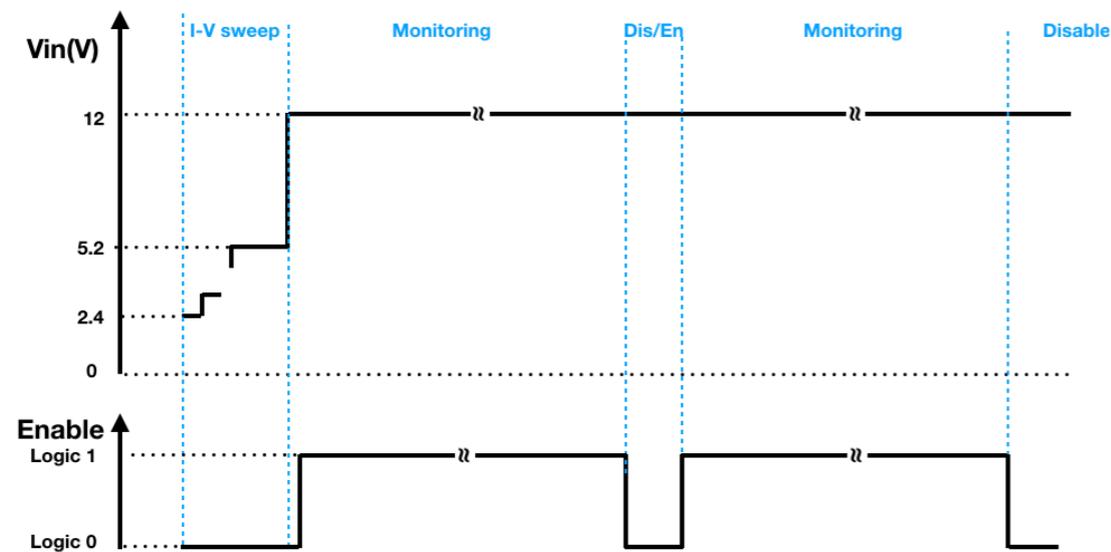
Samples inside the cold box



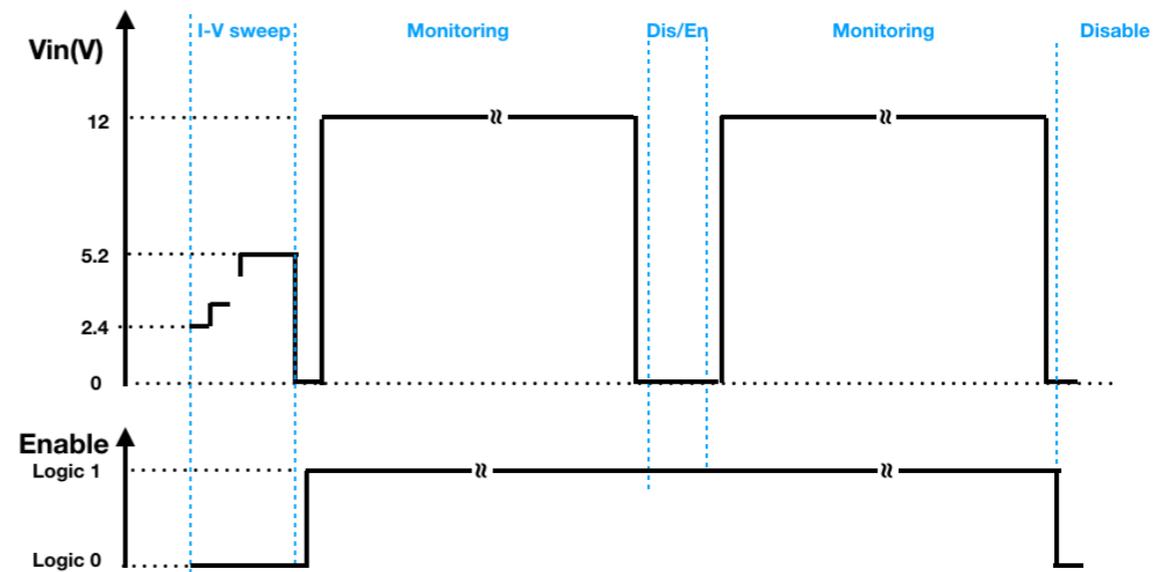
Samples at room T on top of the cold box



- Samples at room T and at -25°C
- New samples and samples survived during the first run
- Samples protected with the addition of a 15kOhm resistor
- Samples protected with the addition of a 3kOhm resistor
- Samples biased with a Vin of 8V (versus 12V for all others)
- Samples without disable/enable sequence (turned off decreasing Vin)
- Half of the samples had the enable input protected by an RC filter



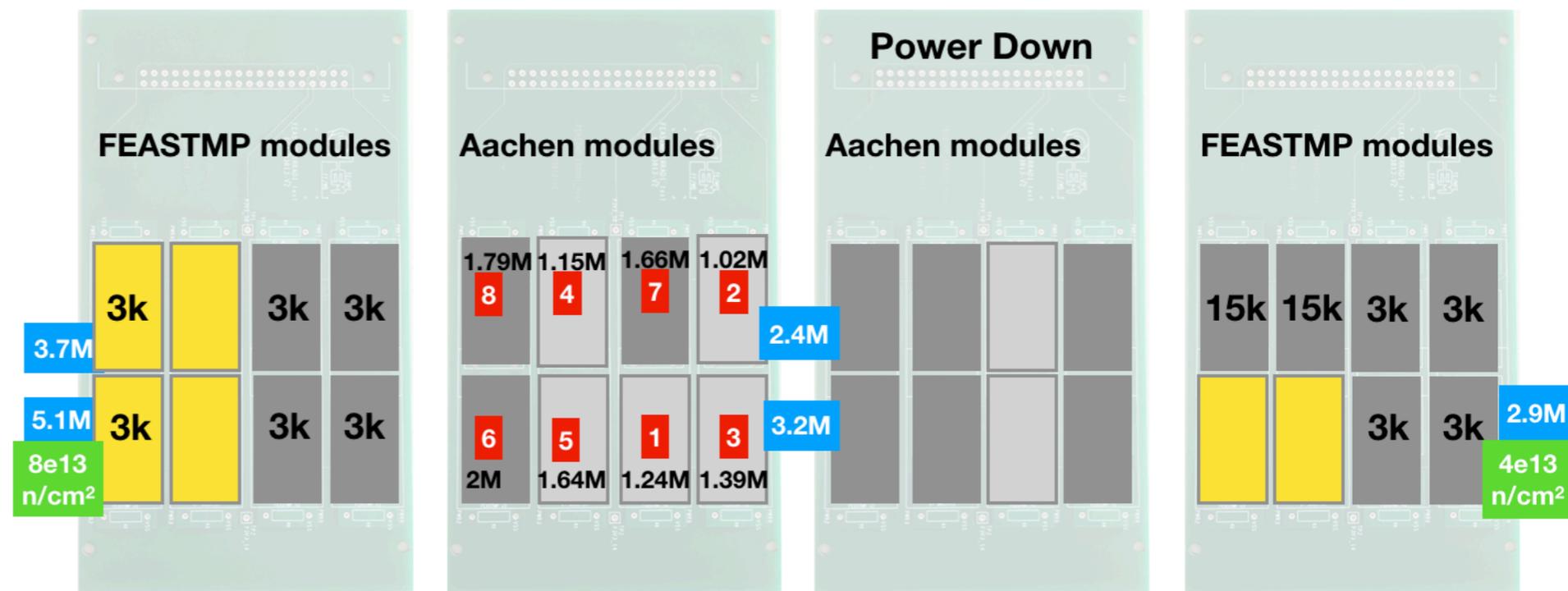
Sequence used during the first run



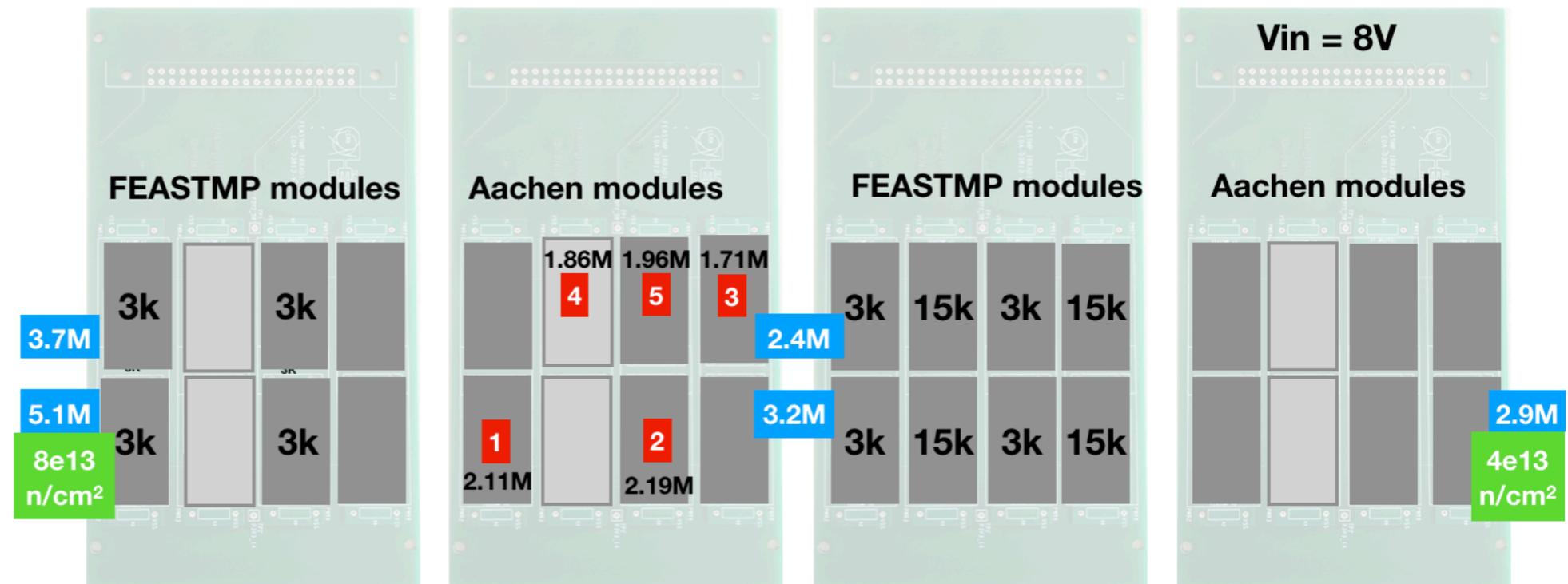
*Sequence avoiding the disable/enable at high Vin
Applied ONLY to 8 converters during the second run*

The results were well in agreement with our expectations

Color code:
 Dark grey = FEAST2.1 new
 Light grey = FEAST2.1 from run1
 Yellow = bPOL12V
 Protection resistor if indicated



Inside the box, T=-25°C



Outside the box, room T

Summary of the observations during the second run

- Samples at room T and at -25°C

 - New samples and samples survived during the first run

 - Samples protected with the addition of a 15kOhm resistor

 - Samples protected with the addition of a 3kOhm resistor

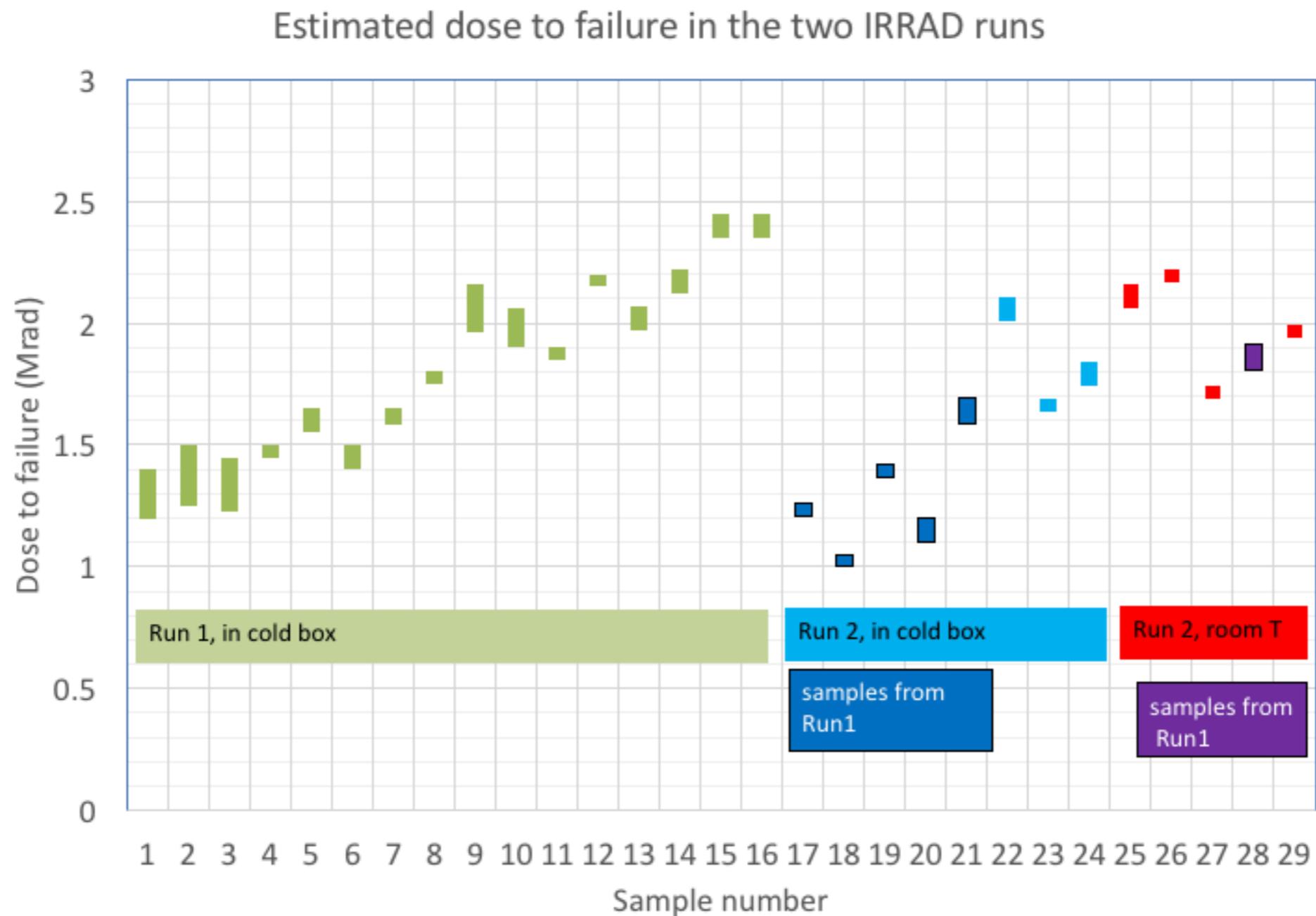
 - Samples biased with a Vin of 8V (versus 12V for all others)

 - Samples without disable/enable sequence (turned off decreasing Vin)

 - Half of the samples had the enable input protected (RC filter)

- Worse damage when cold
- Damage earlier if pre-exposed
- No damage

Summary of the best estimate for the dose to failure for the two IRRAD runs



Damage only occurs above 1Mrad in these high-dose-rate (and low-T) experiments

A revised version of the ASIC (FEAST2.2) to remove the damaged transistors

In February 2018 we have modified the design of the ASIC to remove the “weak” low-voltage transistors from the V33Dr node, as well as to add a dedicated ESD protection device to the pad.

- this was meant to eliminate the “broken” type of damage (only “High-current” possible)
- additionally, this could have helped the node to resist a hypothetical aggression (discharge?)

